

Electron Transport in Strongly Coupled Molecular Electronic Junctions

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National Institute for Nanotechnology

NRC-CNRC



UNIVERSITY OF
ALBERTA



**NSERC
CRSNG**



Canada Foundation for Innovation

National Institute for
Nanotechnology
University of Alberta,
Edmonton, Alberta,
Canada

Founded 2002
Building dedicated 2006

\$\$\$:

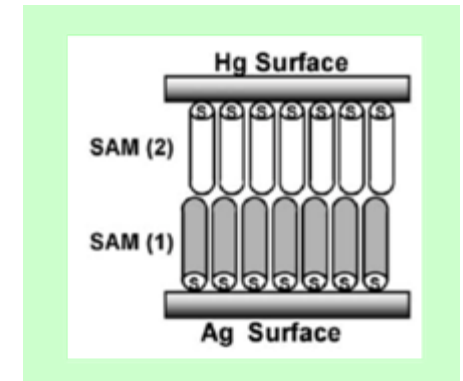
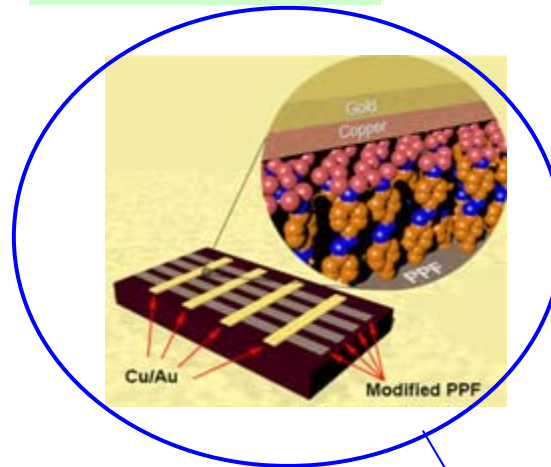
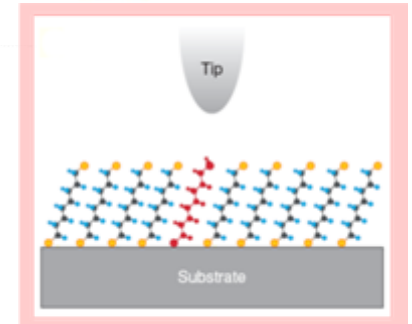
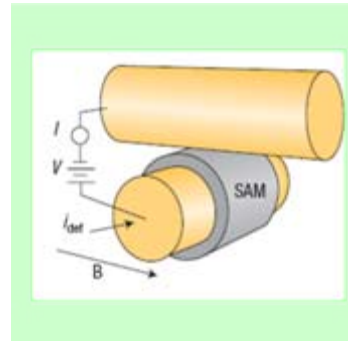
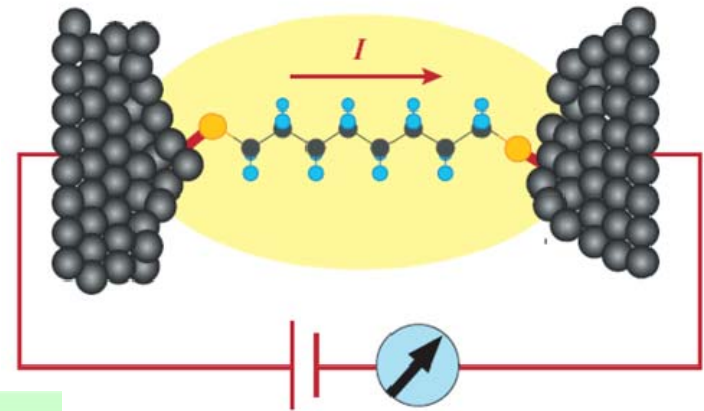
National Research Council
NSERC (Canada)
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“Molecular electronics”



“molecular junctions:”

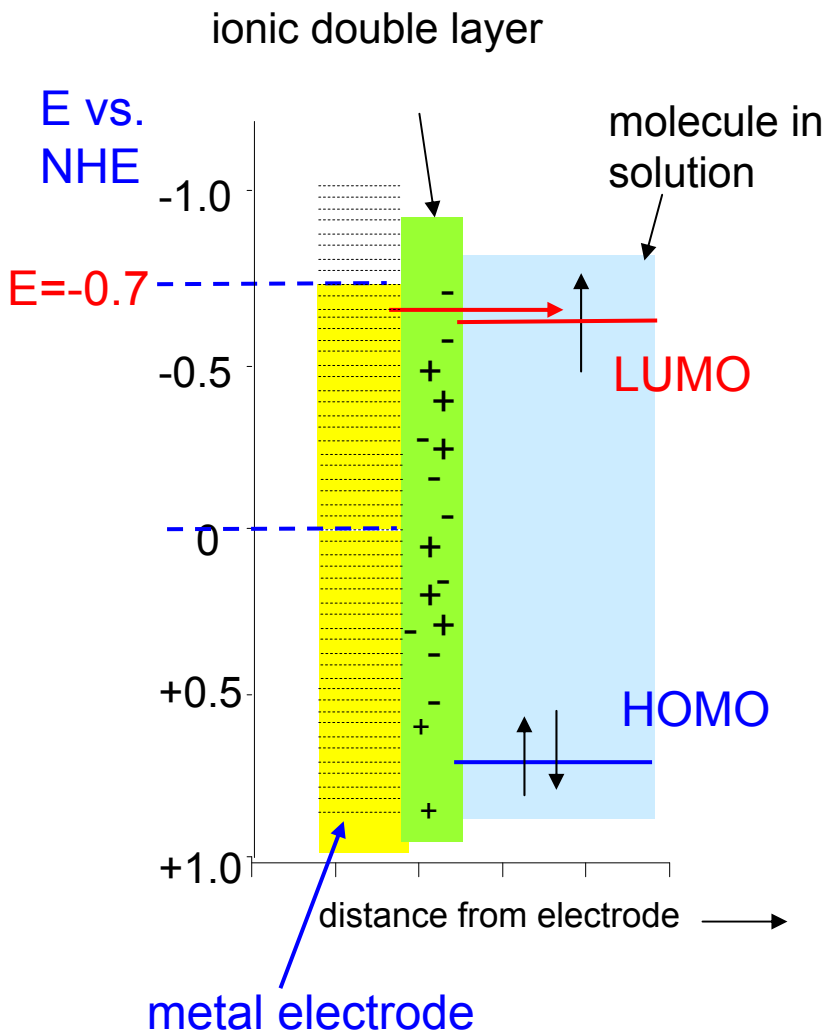


Note:

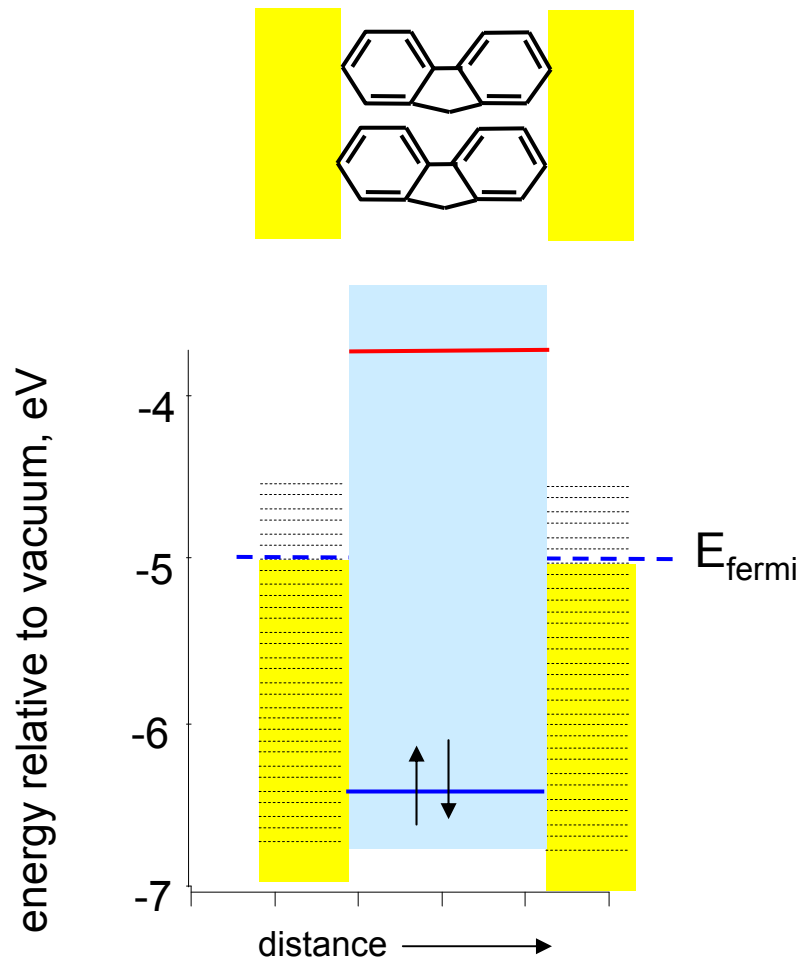
- molecules become circuit elements
- critical dimension is 1-10 nm

Today's question: How are electrons transported through molecules ??

Electrochemical reduction:



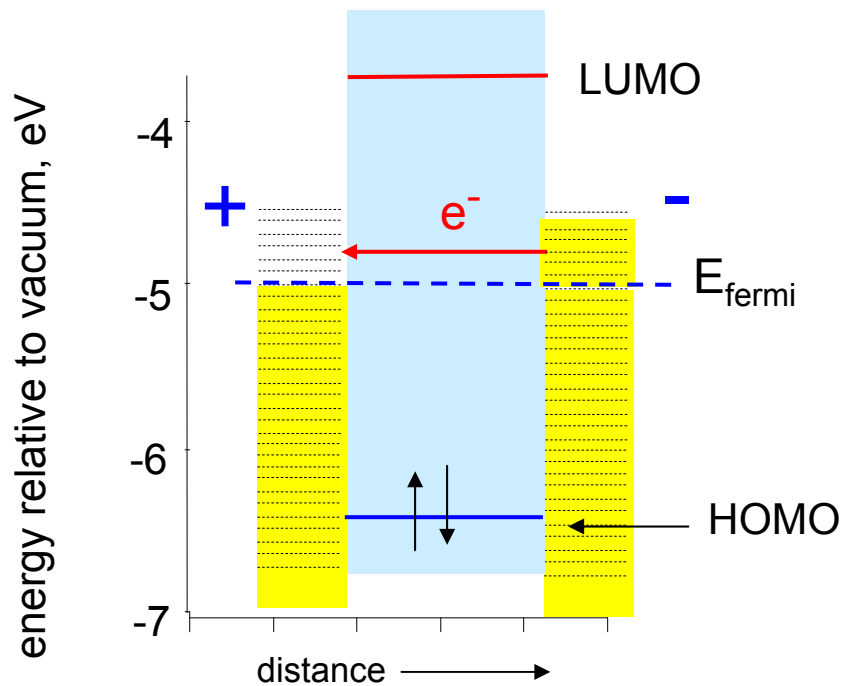
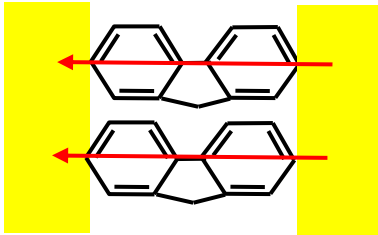
Molecular junction:



two electrodes, no double layer, no solution

Two common electron transport models:

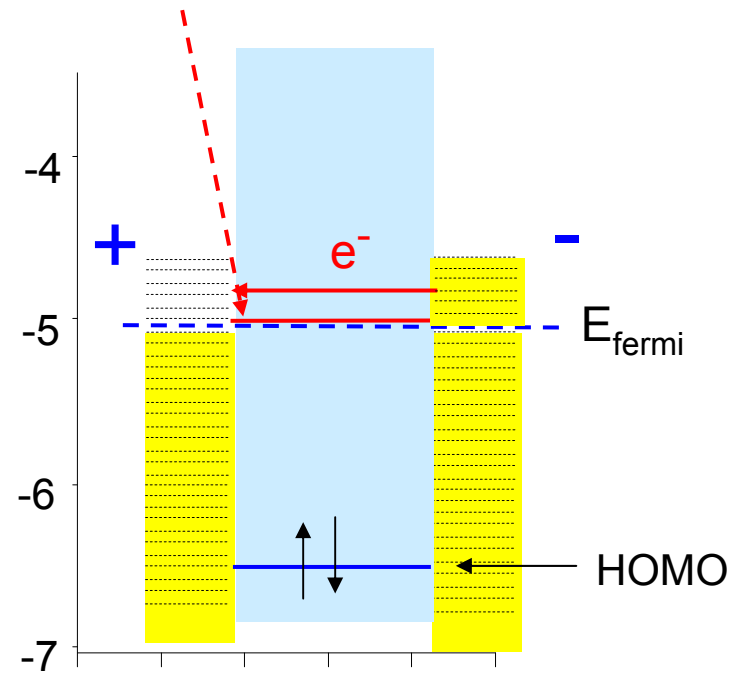
“off-resonant”



e.g. tunneling, Schottky,
field emission

“resonant”

LUMO is close (\sim within kT)
to Fermi level



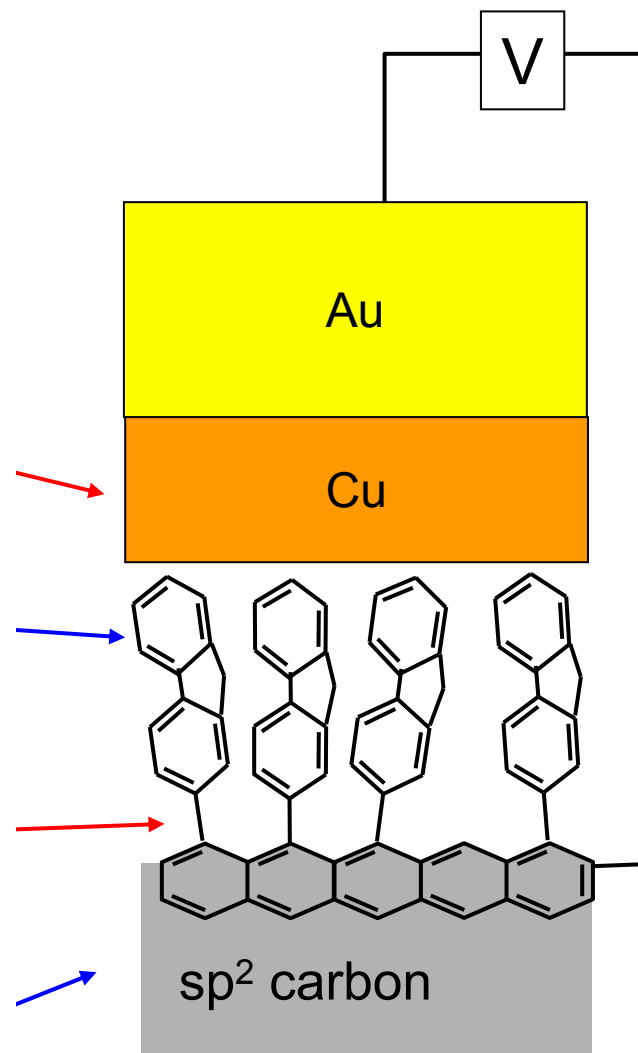
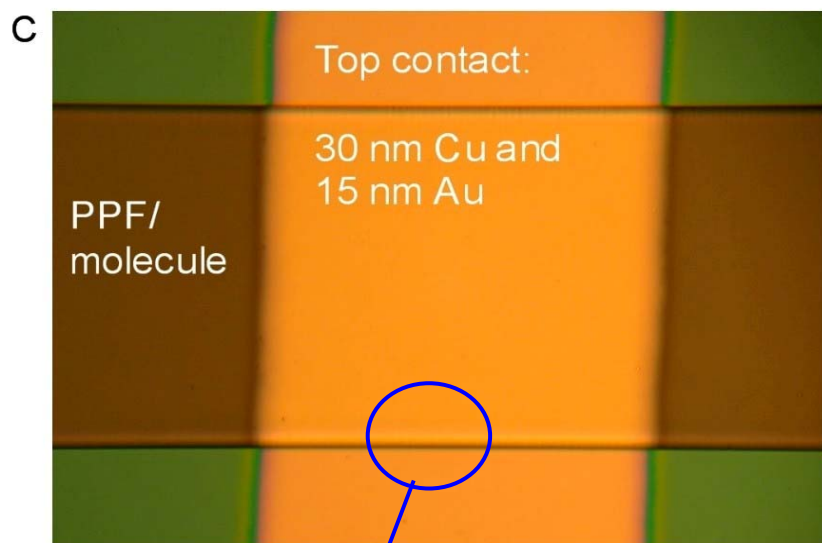
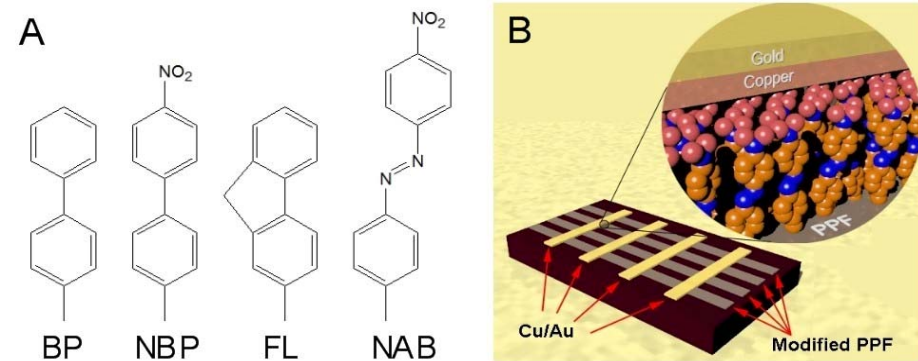
e.g. “resonant tunneling”,
“orbital mediated tunneling”

The scientific question:

How are electrons transported through 1-5 nm thick molecular layers?

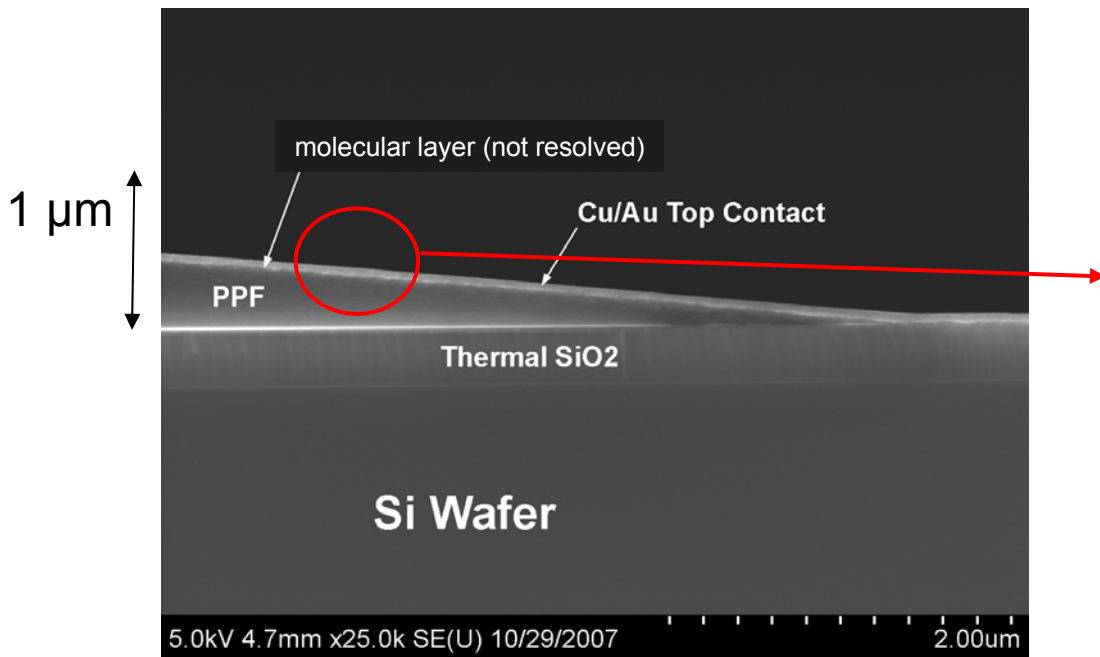
Outline:

- fabrication of molecular junctions
- characterization
- electronic properties
- transport mechanism

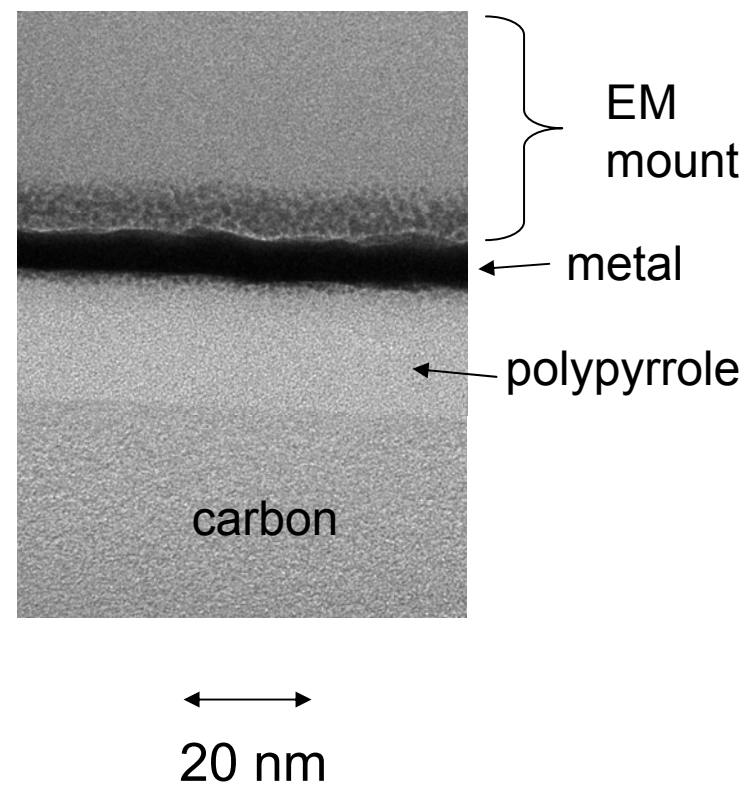


Phys. Chem. Chem. Phys., **2006**, 8, 2572
J. Chem. Phys. **2007**, 126, 024704
J. Phys. Cond. Matter, 20, 374117 (2008)

SEM

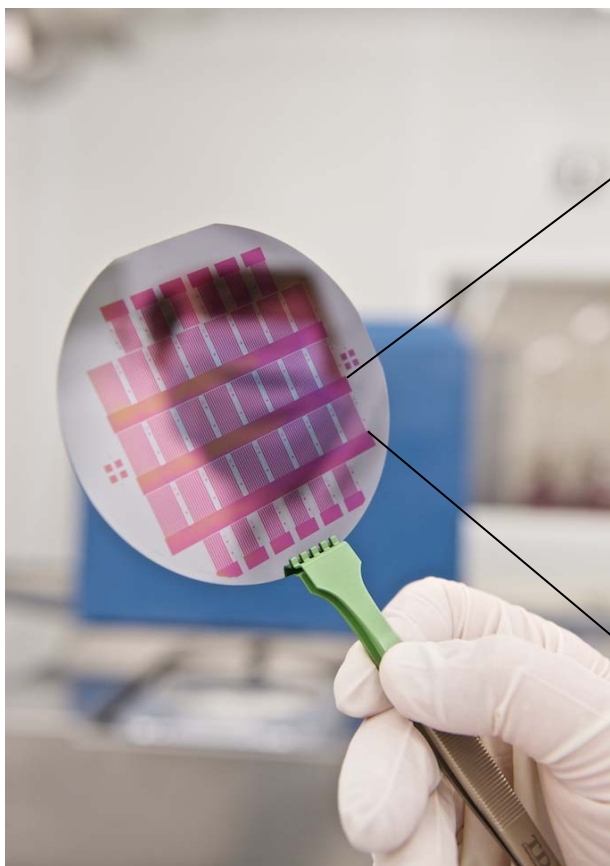


TEM

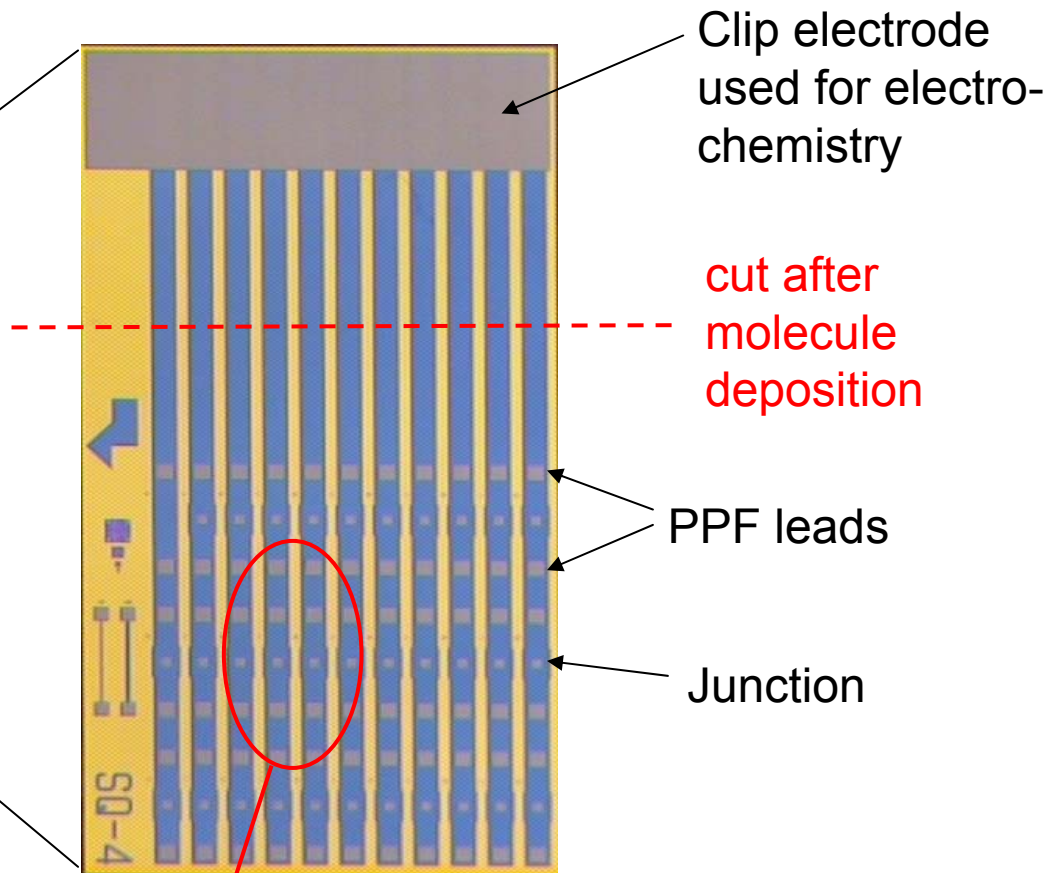


Microfabricated "E-chips"

PPF Echip 4" wafer

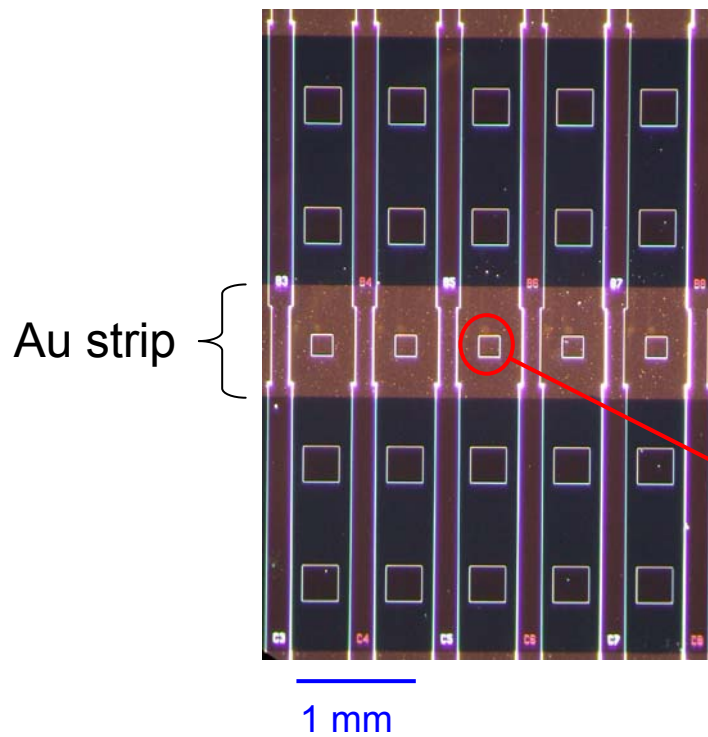


PPF Echip



next slide

Bryan Szeto
Jie Ru



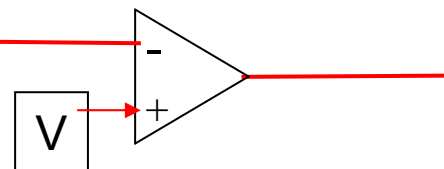
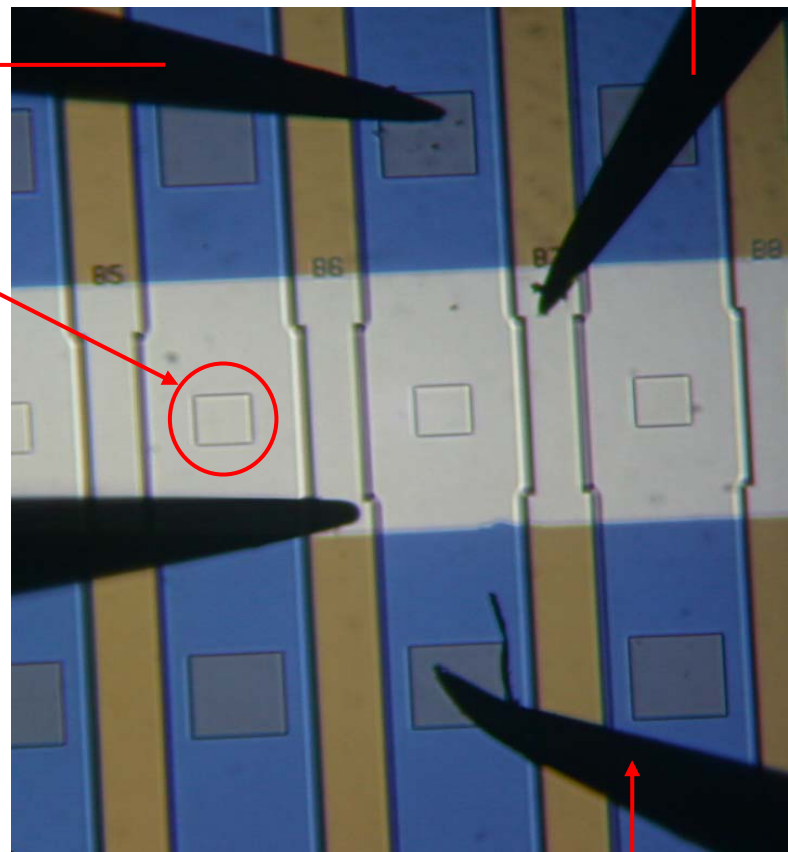
Junction area:

2.5 x 2.5 μm to
400 x 400 μm

V_{sense}

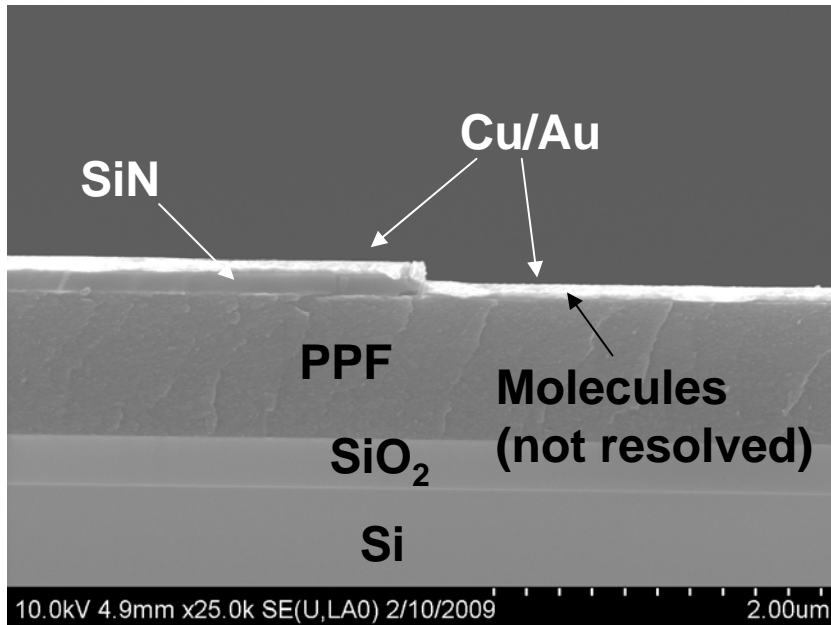
500 μm

current amplifier

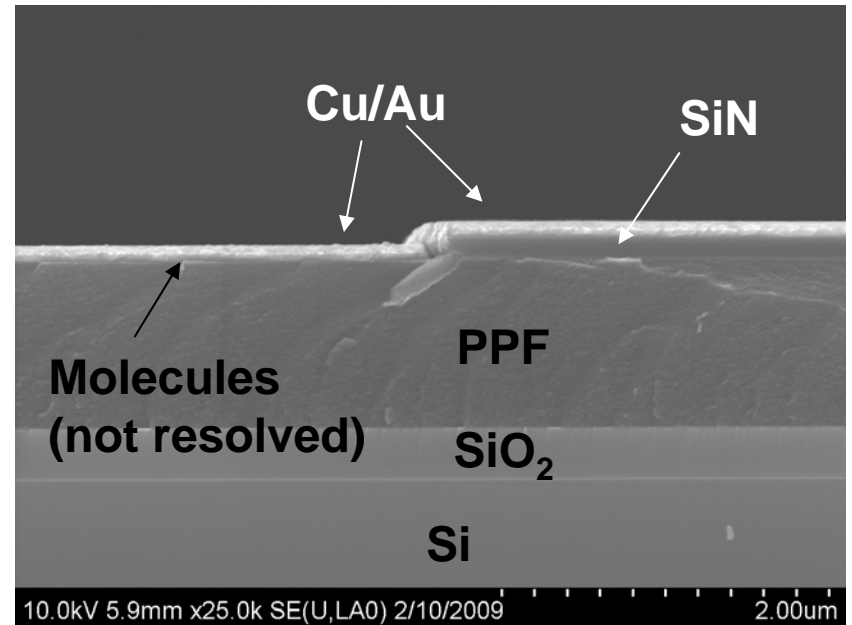


Cross section of a PPF/NAB/Cu/Au junction (SEM)

Left side

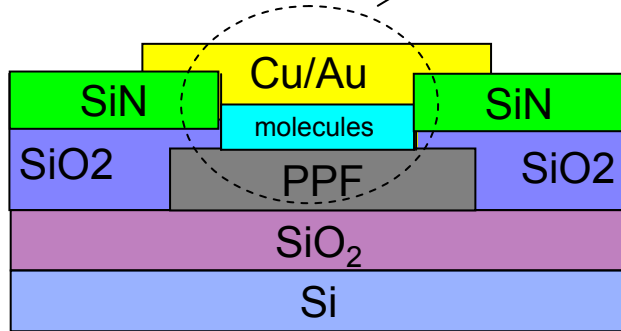
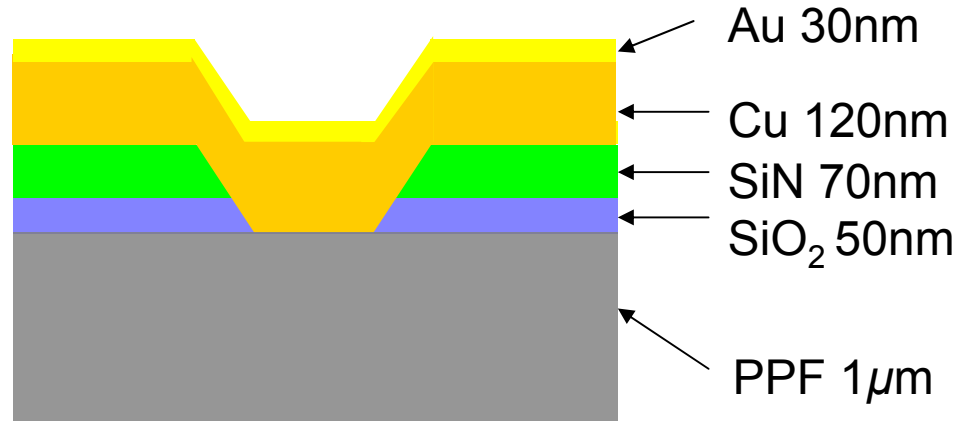


Right side

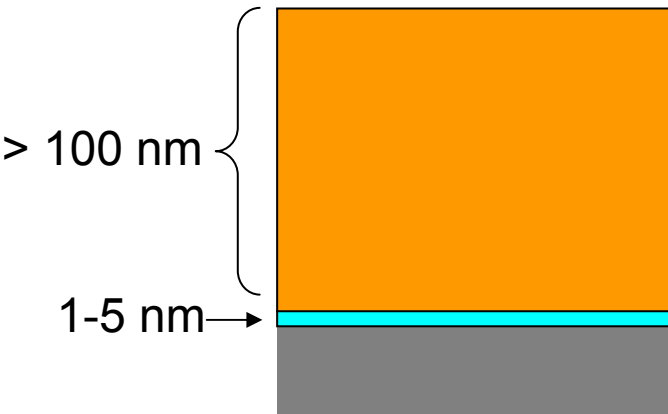
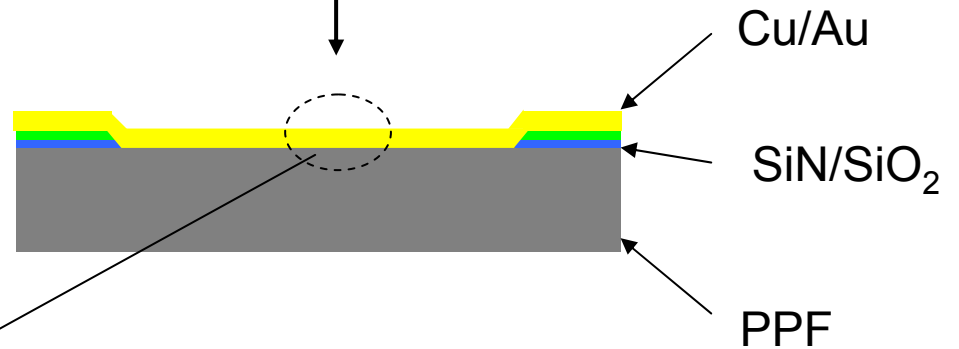


Schematic of junction structure:

(not to scale)

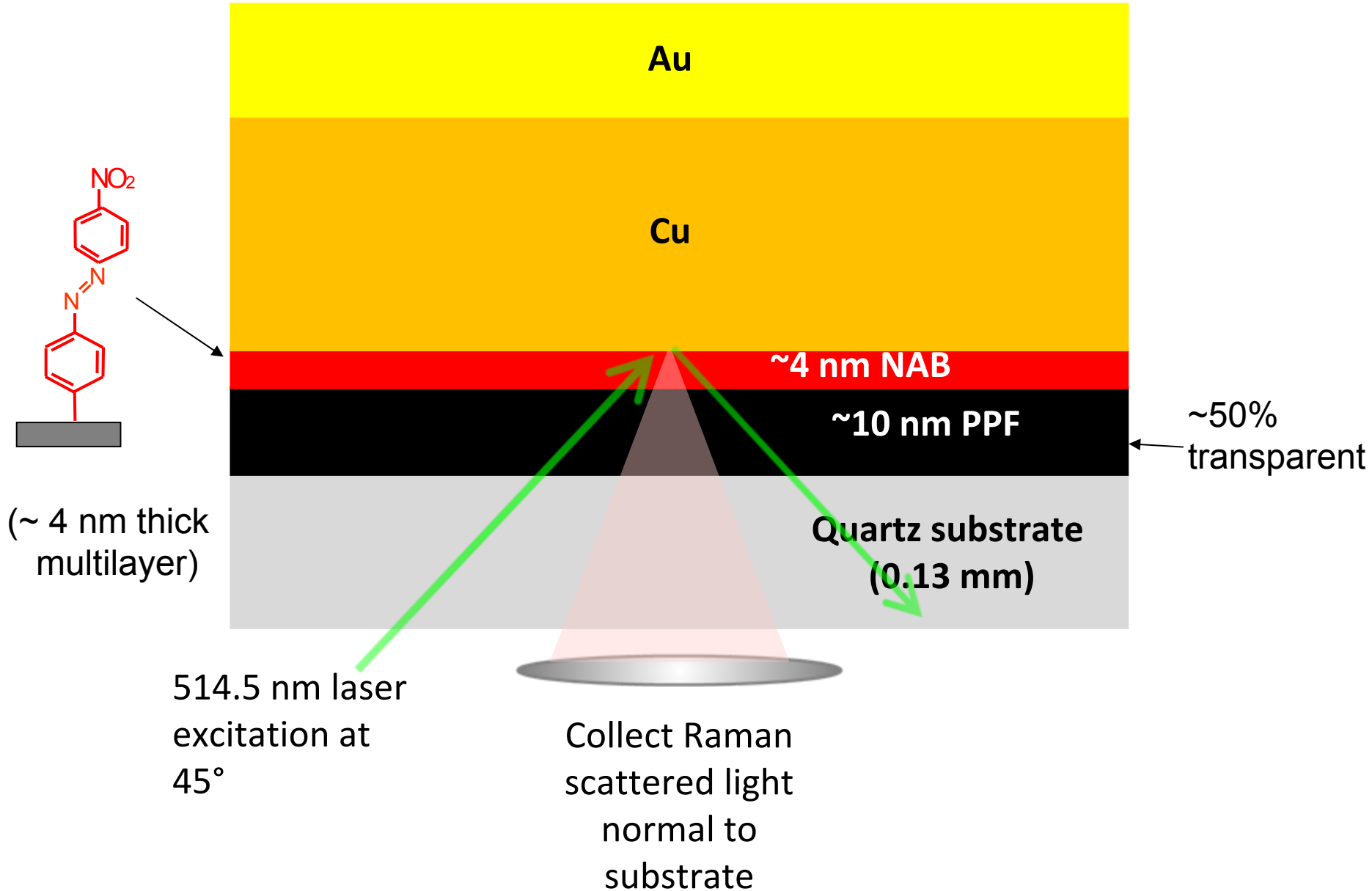


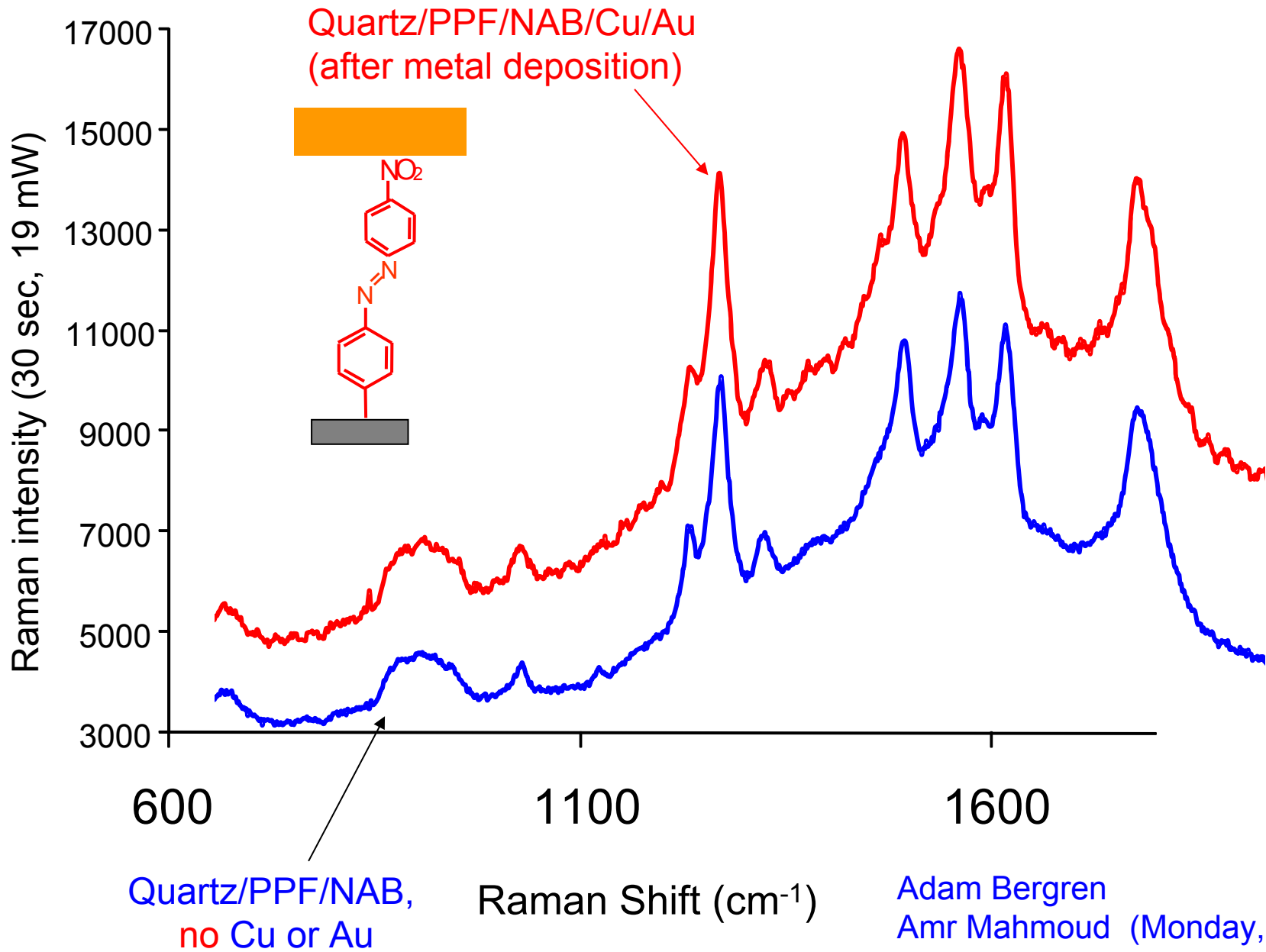
to scale:



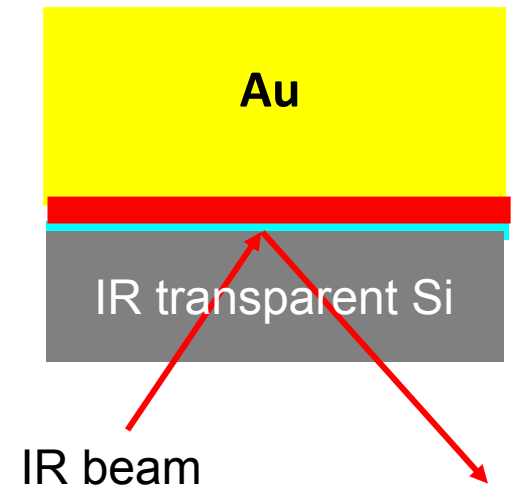
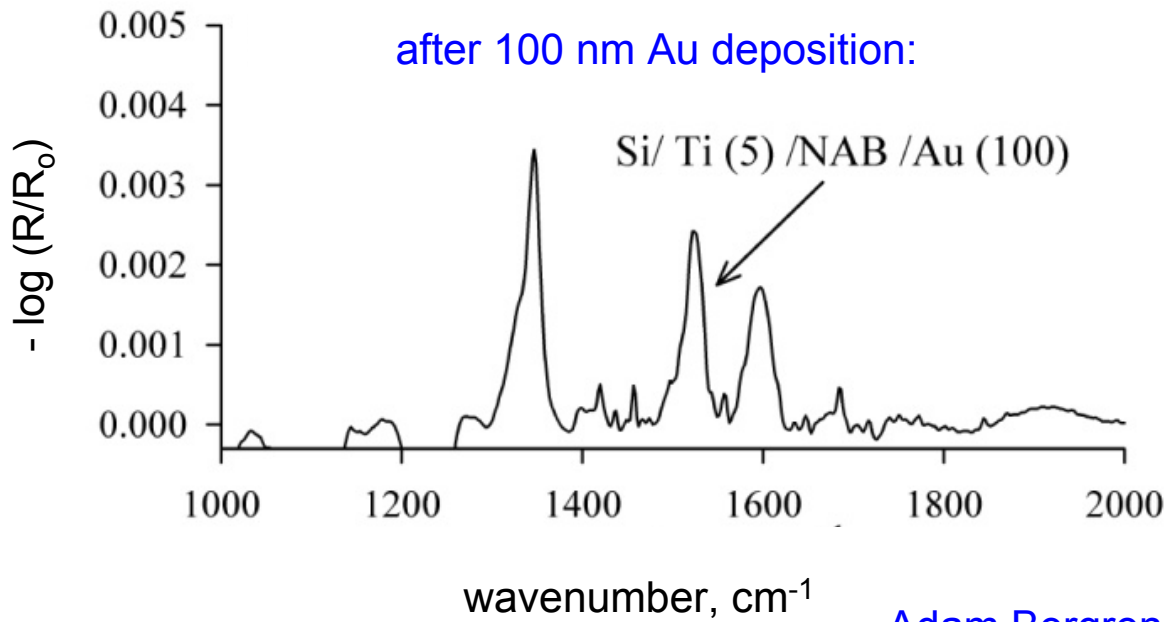
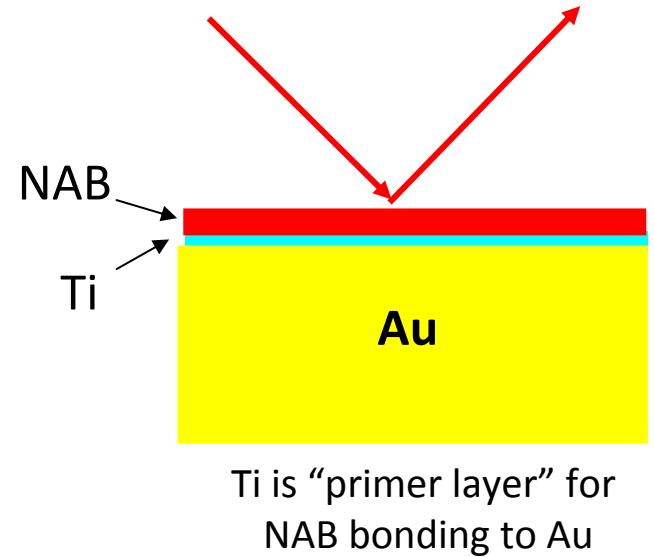
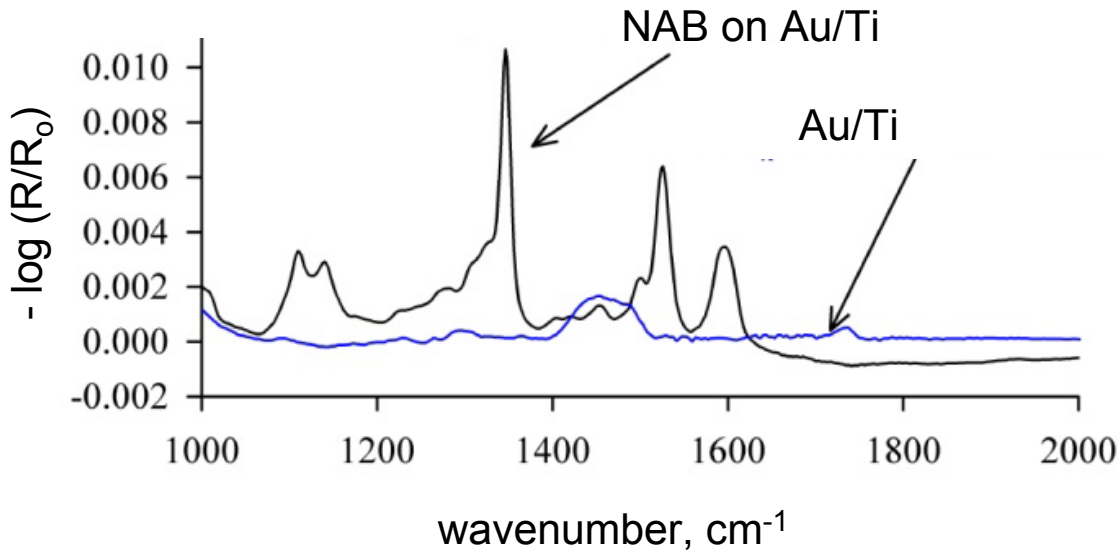
molecular layer is really thin compared to metals, does it survive metal deposition??

“backside” Raman of buried interface:

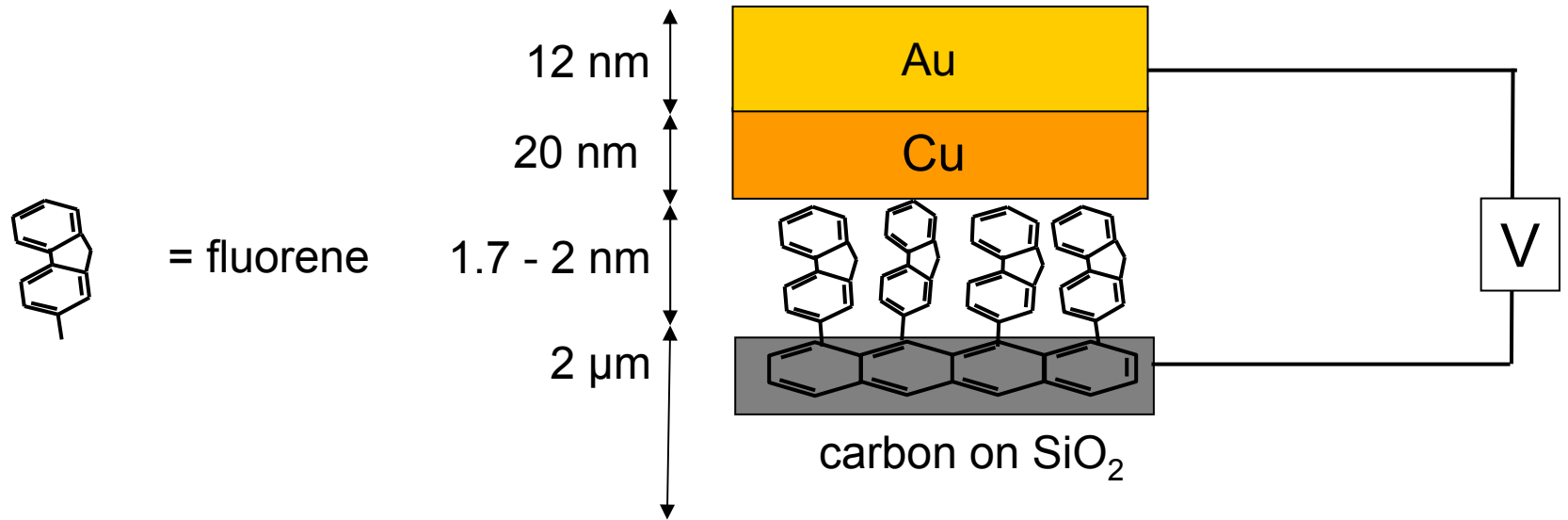
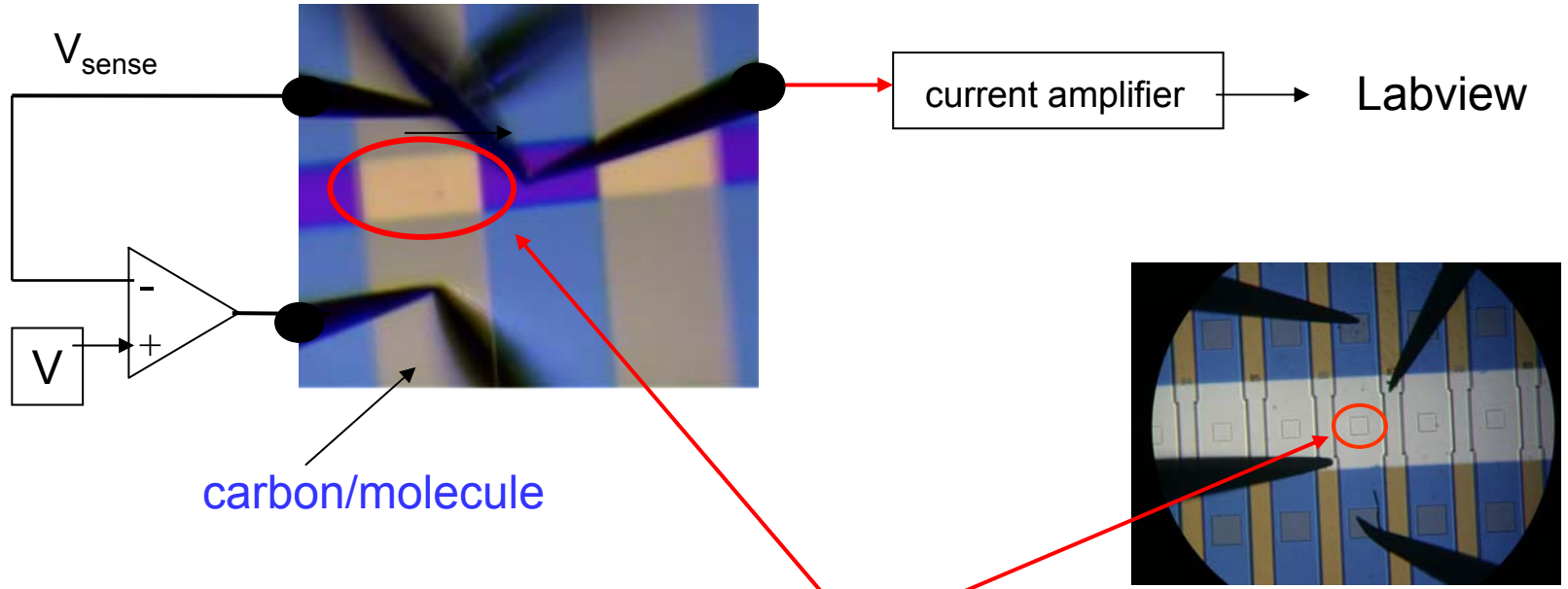




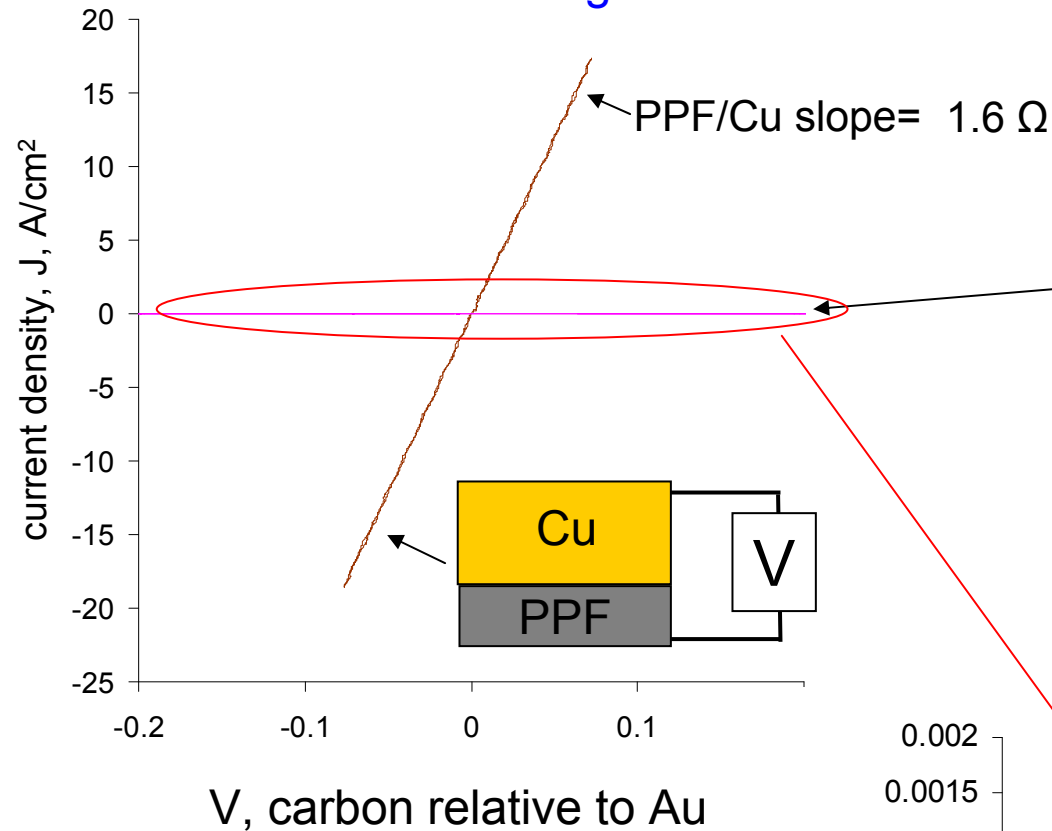
FTIR of buried interface:



Electronic behavior:

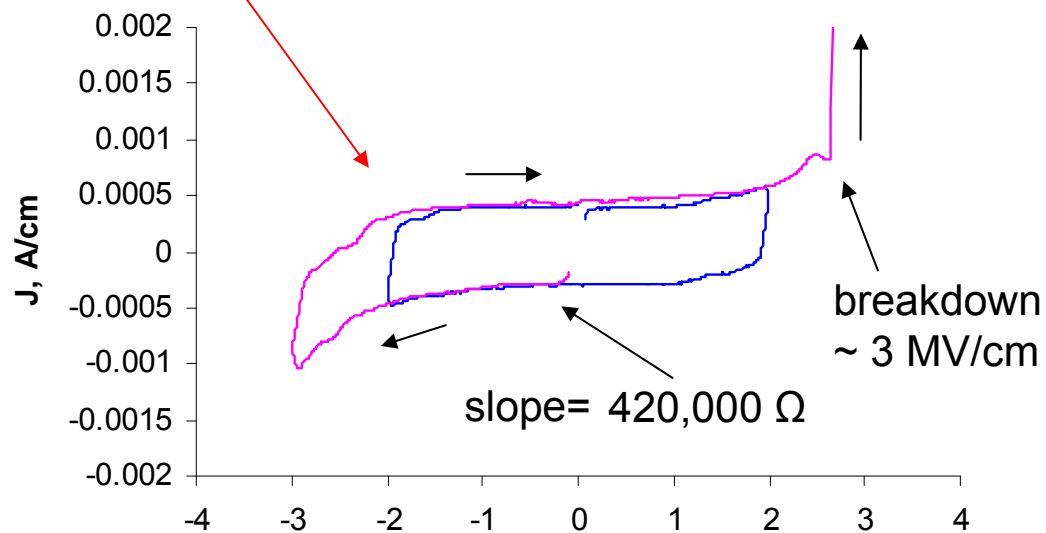
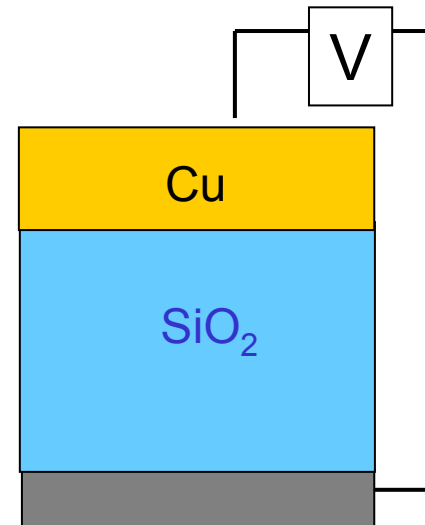


Start with something familiar:

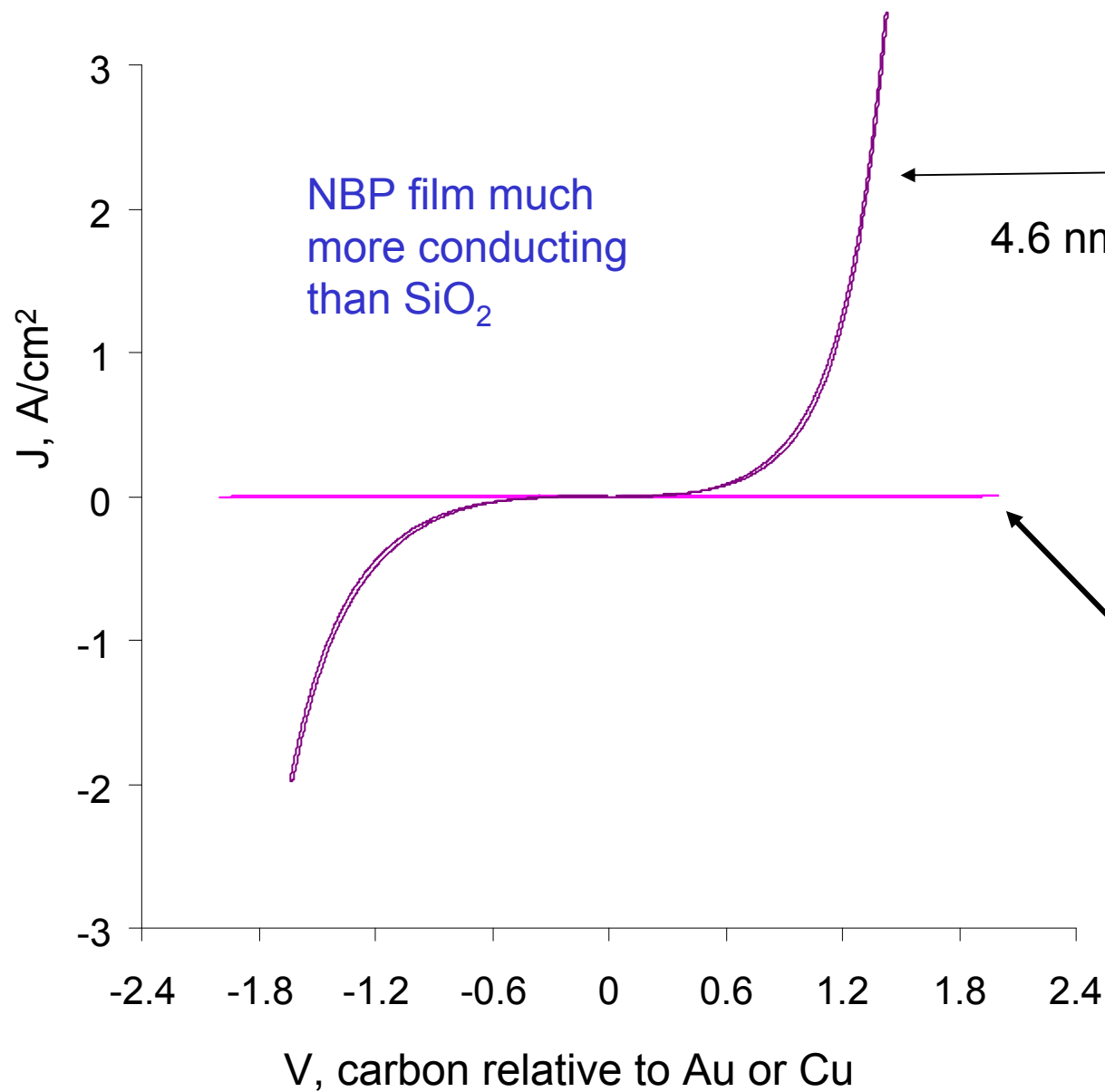


PPF/SiO₂/Cu

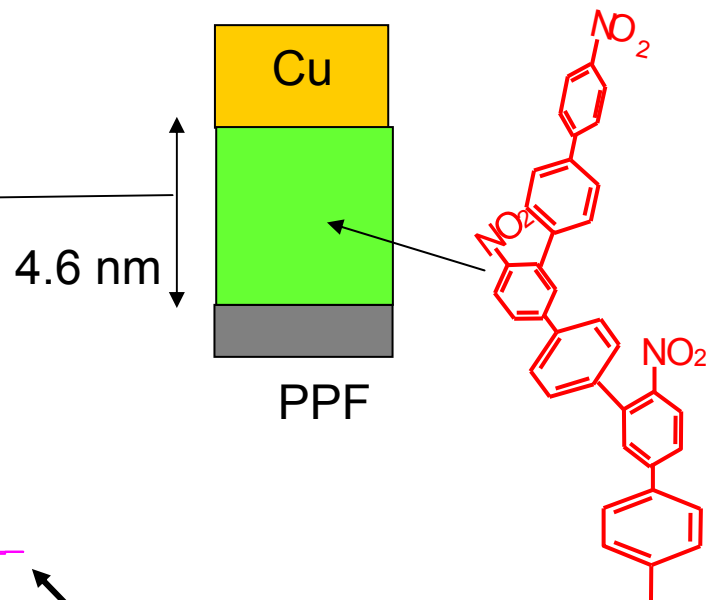
10 nm



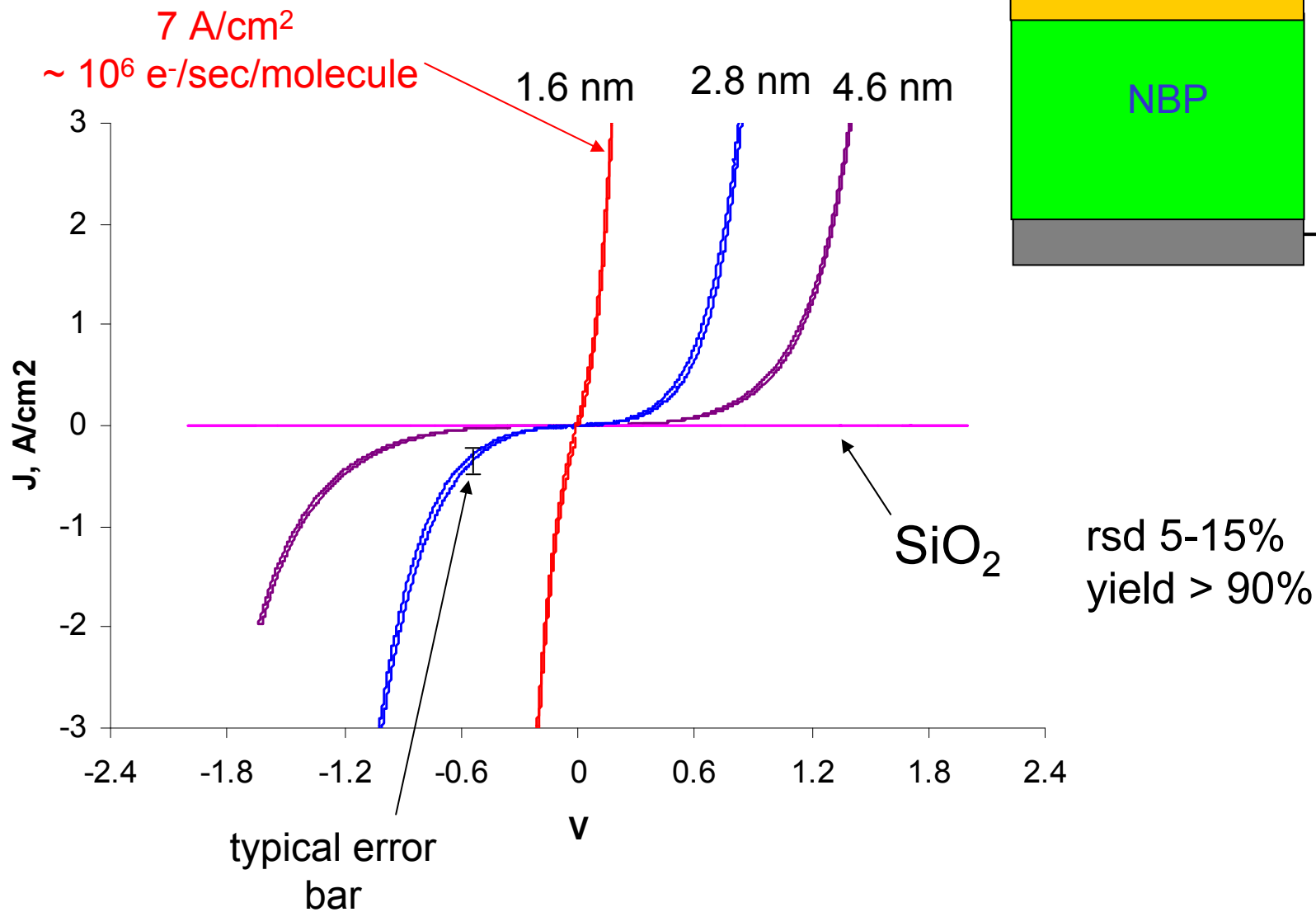
How about a molecule instead of SiO₂ ?



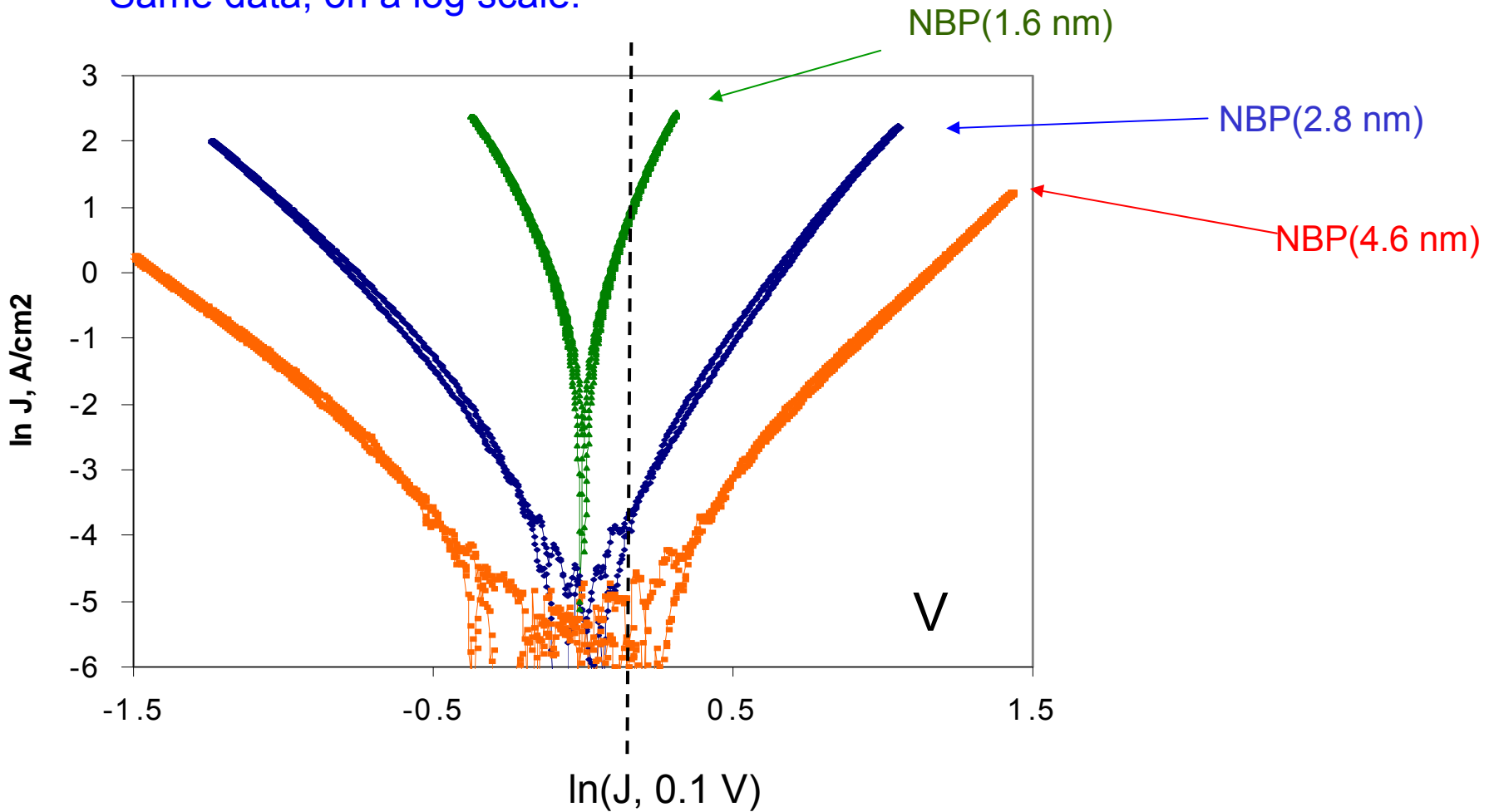
nitrophenyl multilayer
4.6 nm thick:



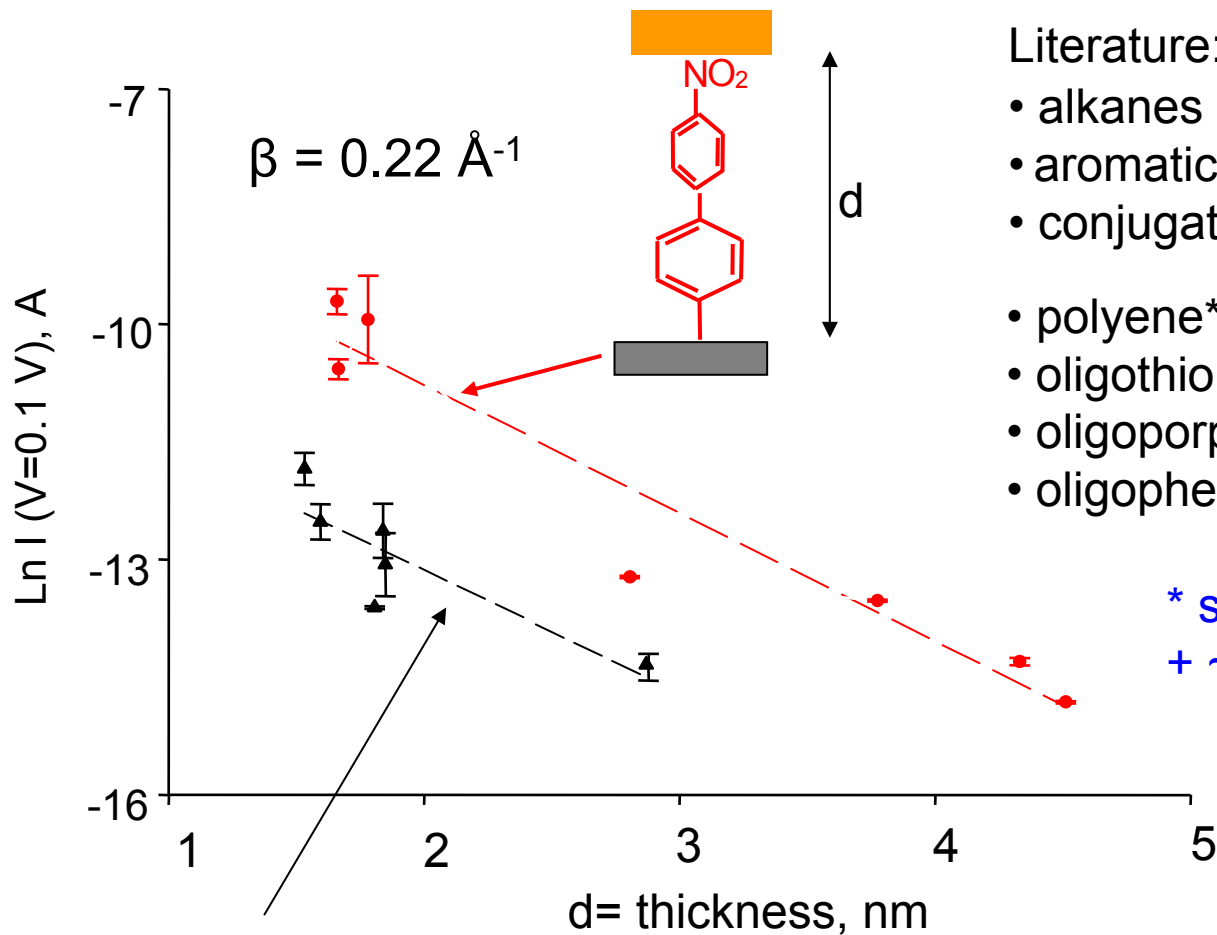
Nitrophenyl junctions of differing thickness:



Same data, on a log scale:



- No obvious shape change from 1.6 to 4.6 nm thickness
- Symmetric with minimal hysteresis
- Repeatable > 10⁸ cycles



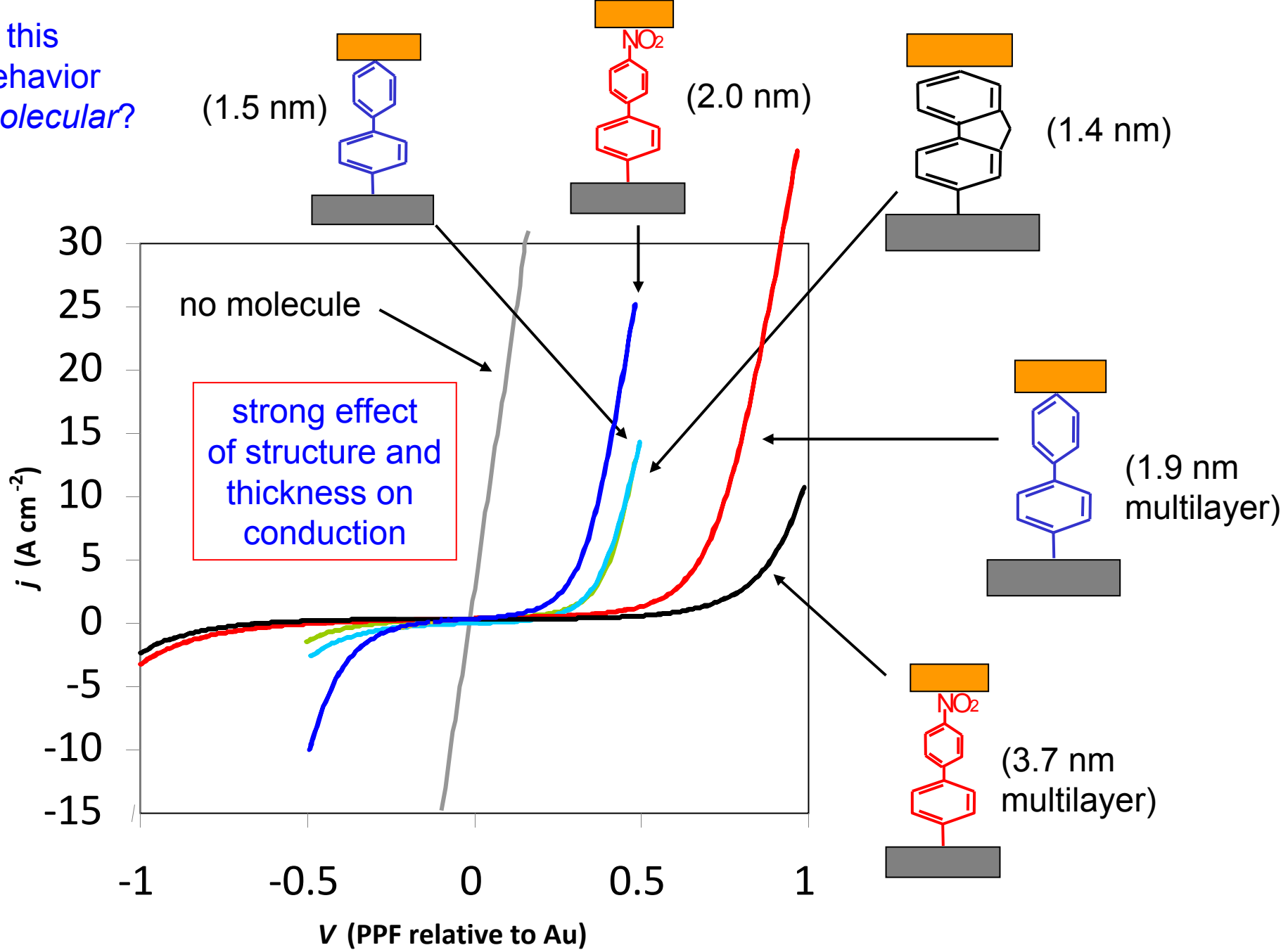
Literature:

- | | β |
|--------------------------------|------------------------|
| • alkanes (echem or junctions) | 0.8 \AA^{-1} |
| • aromatic (echem, 1999) | 0.22 |
| • conjugated (echem, SAM) | 0.3 to 0.6 |
| • polyene* (2005) | 0.22 |
| • oligothiophene* (2008) | 0.1 |
| • oligoporphyrin* (2008) | 0.04 |
| • oligophenyleneimine+ (2008) | 0.3 |

* single molecule junction
+ ~100 molecule junction

β is smaller for aromatic structures
(i.e. conjugated molecules are
better “conductors”)

Is this behavior *molecular*?



Various transport mechanisms:

Weakly Temperature dependent:

Coherent tunneling, "superexchange"

Incoherent, diffusive tunneling

Field emission (Fowler Nordheim)

distance dependence:

$$\exp(-\beta d)$$

$$\exp(-\beta' d)$$

$$(V/d) \exp(-a d)$$

Strongly Temperature dependent ("activated"):

Thermionic (Schottky) emission

Poole-Frenkel effect ("coulombic traps")

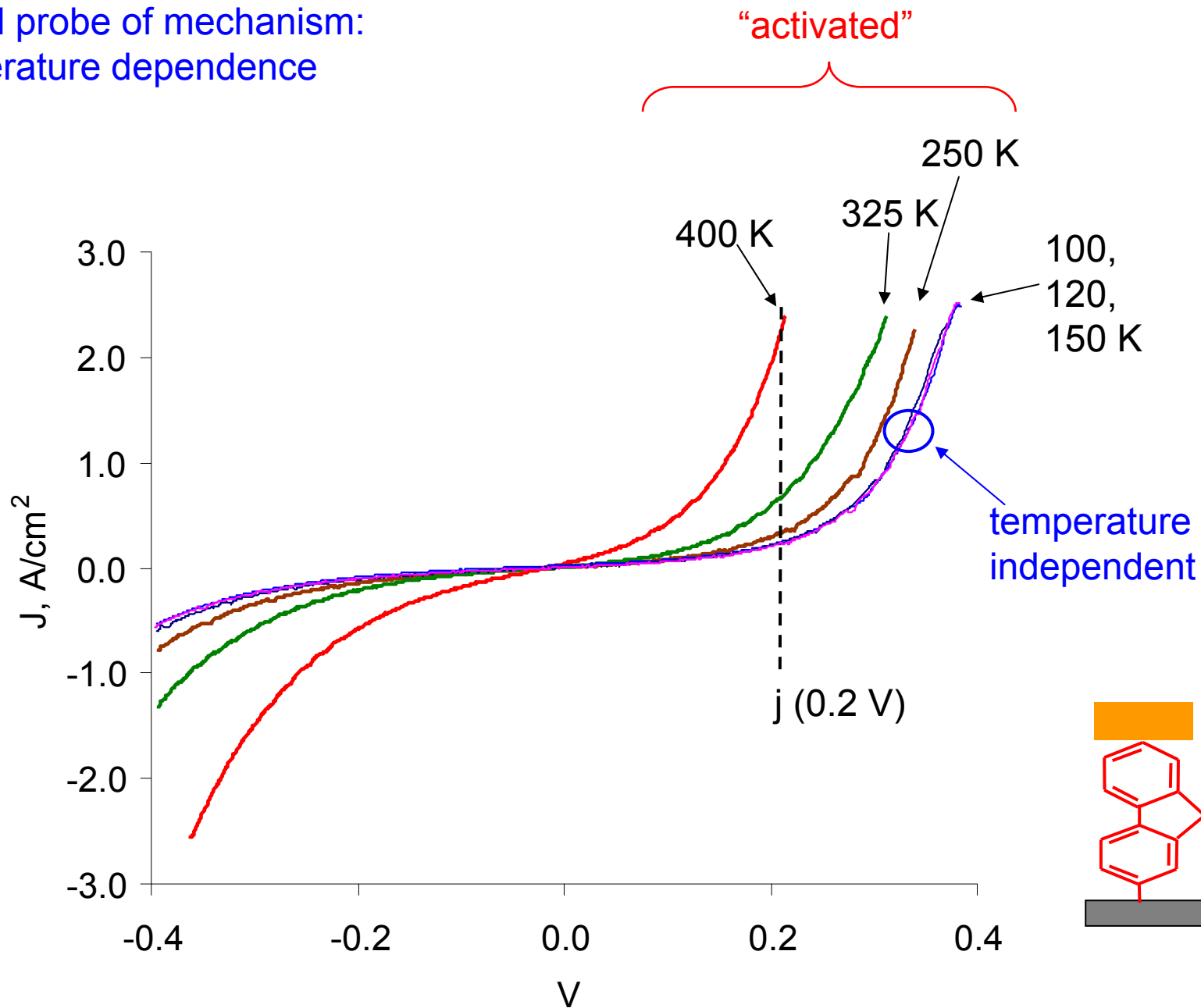
"hopping", including redox exchange
(Marcus-Levich)

$$\exp(-c d^{1/2})$$

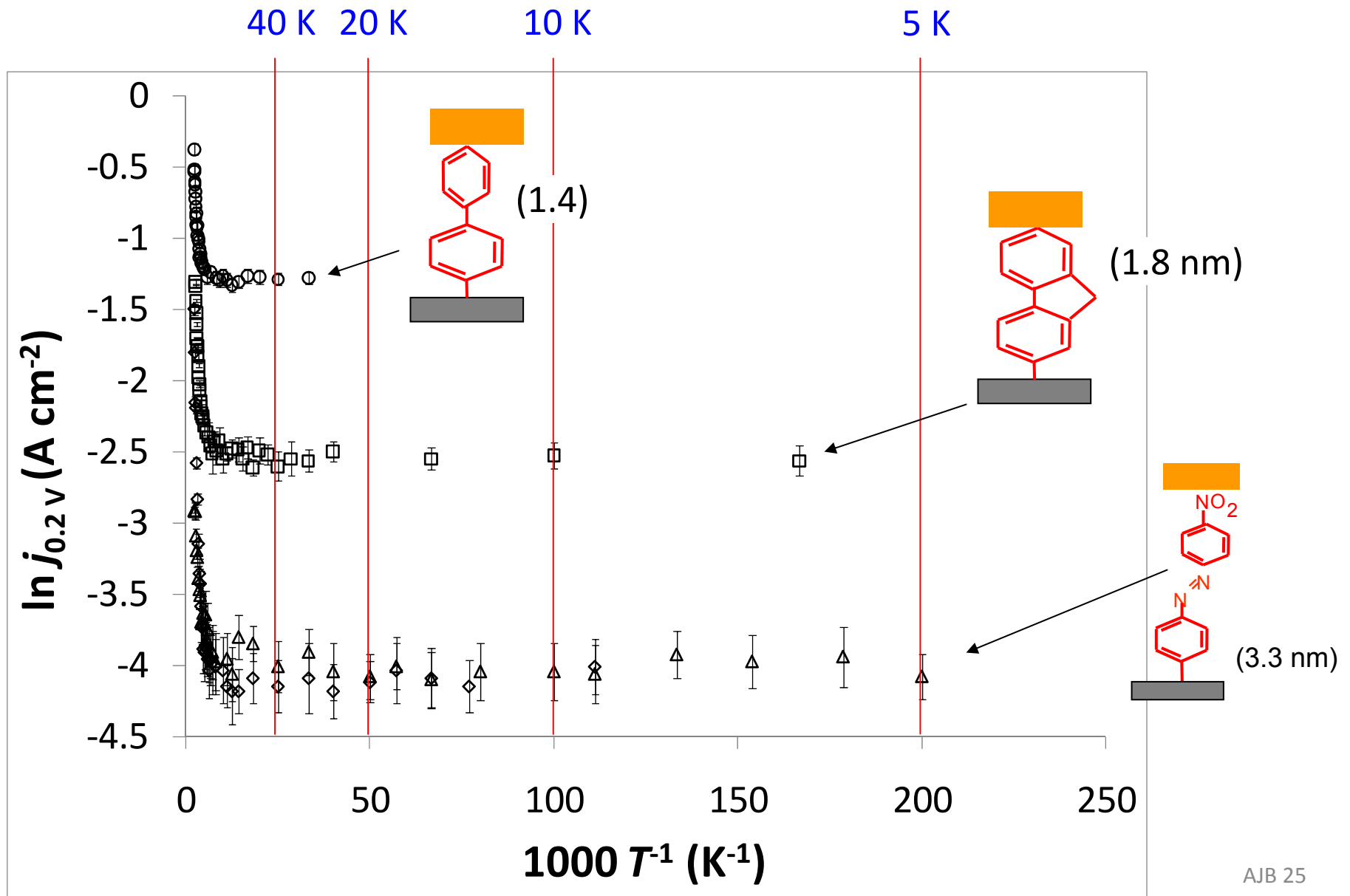
$$\exp(-c' d^{1/2})$$

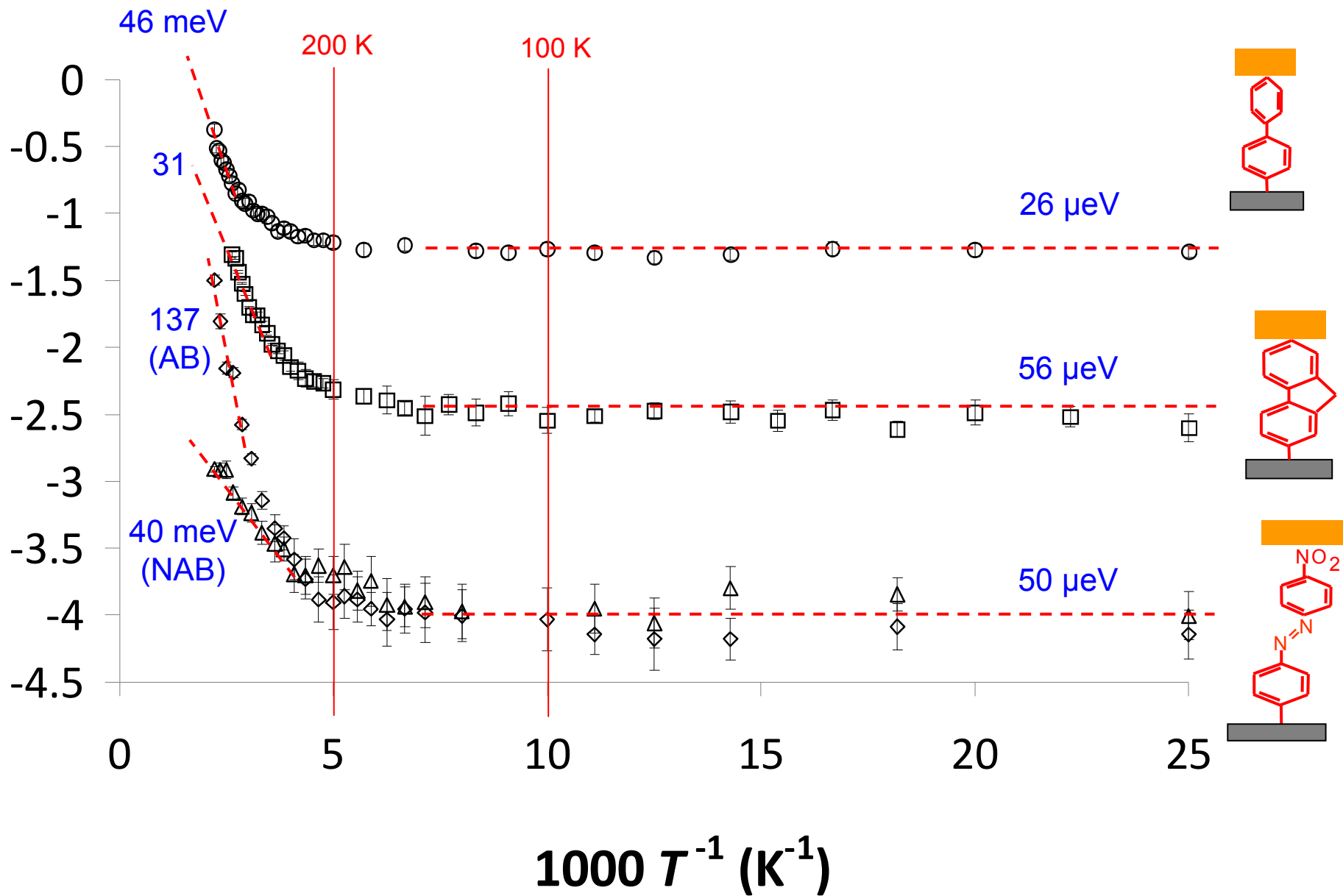
$$d^{-1}$$

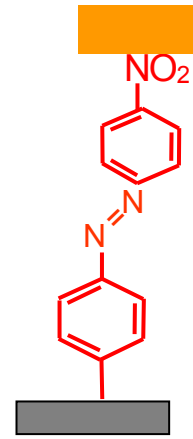
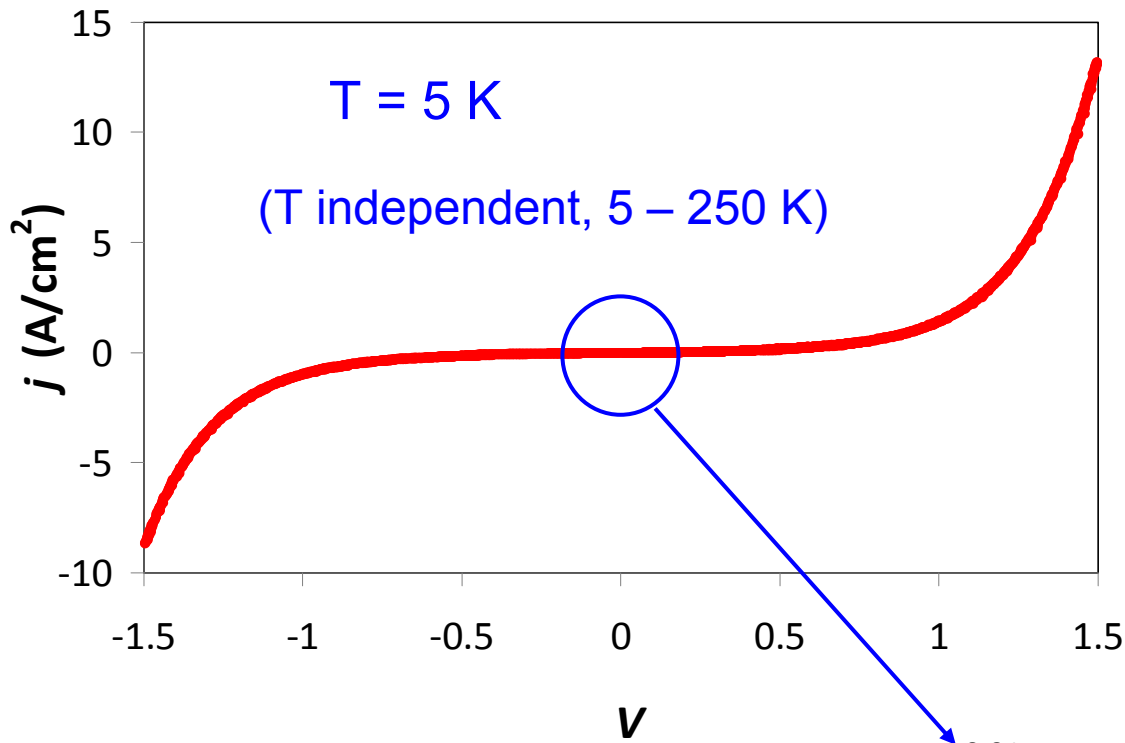
A good probe of mechanism:
Temperature dependence



Arrhenius plots



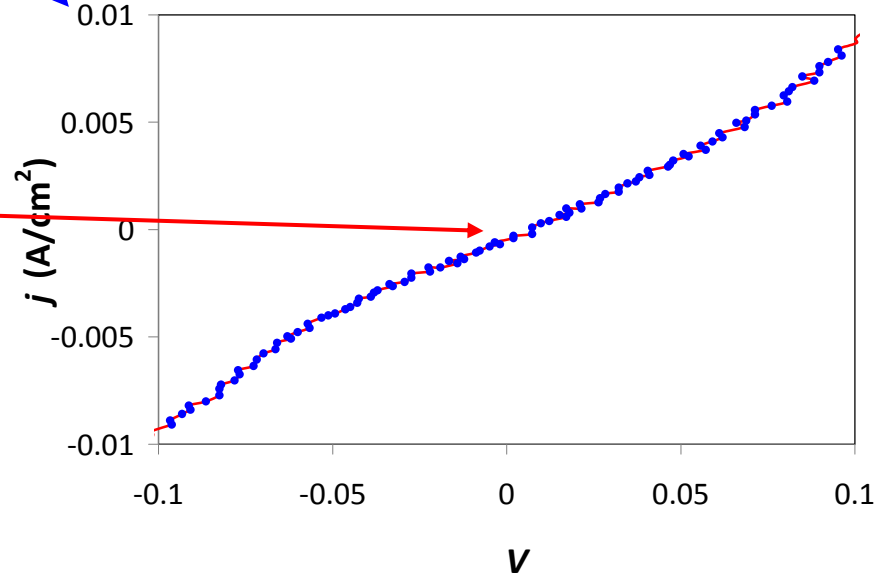




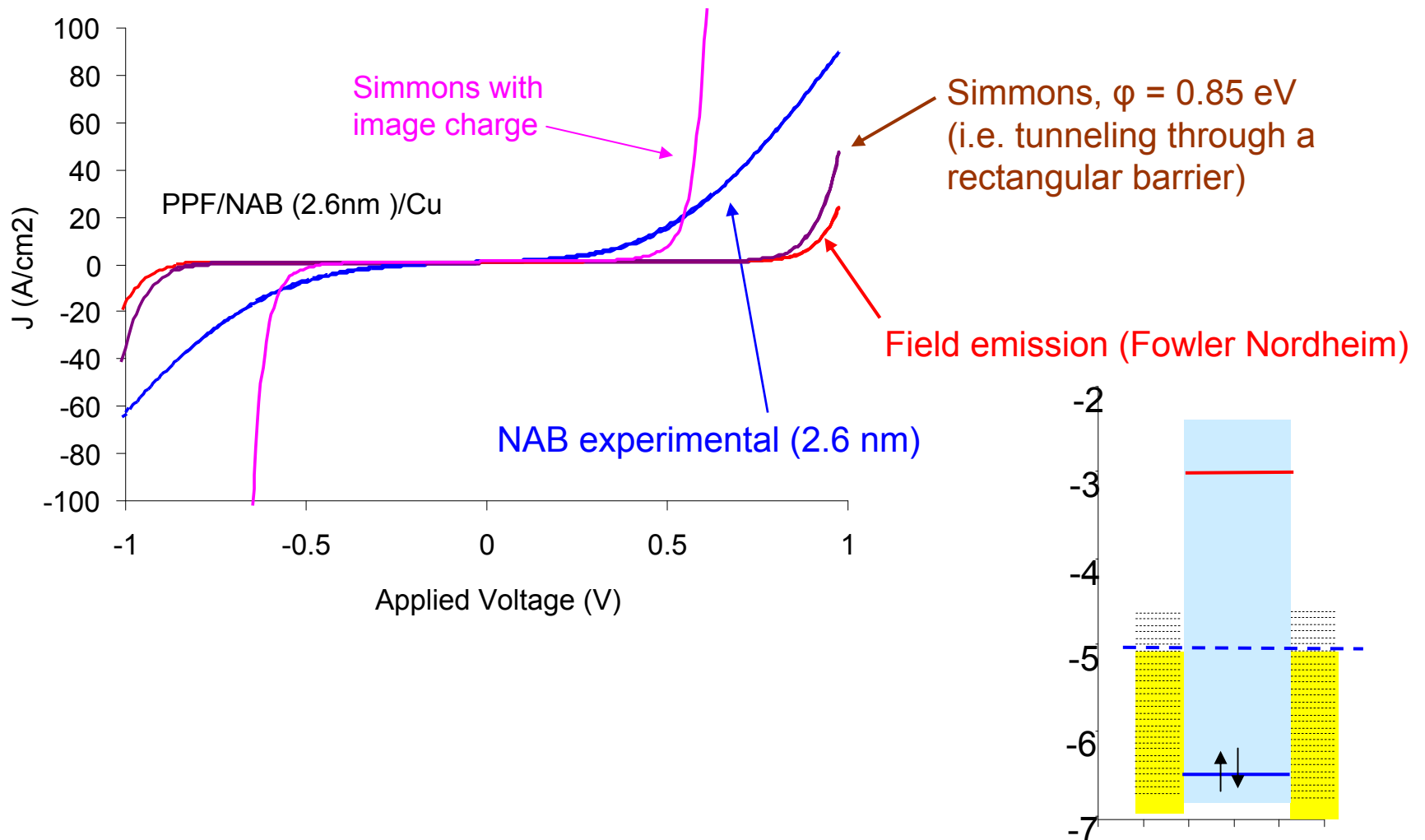
(4.5 nm multilayer)

need to explain:

- apparent ohmic contact
- T-independent, despite:
- 4.5 nm thick (too thick for tunneling)



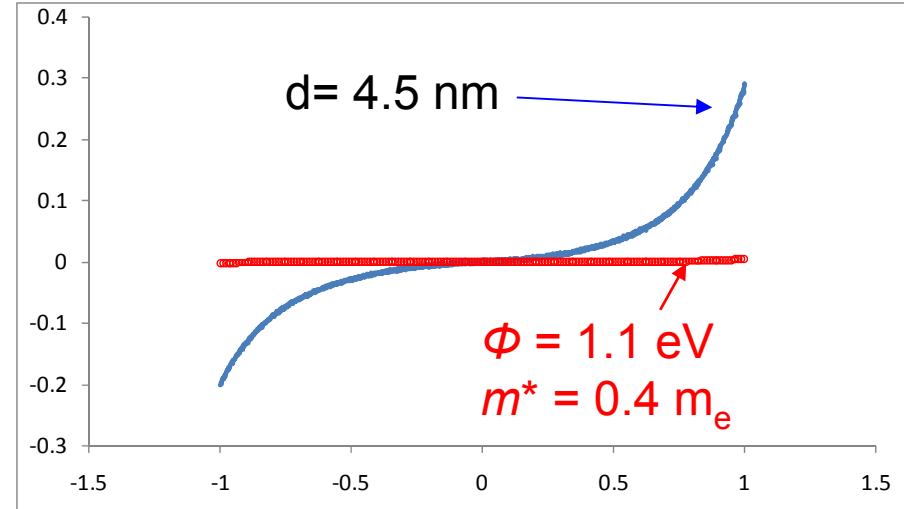
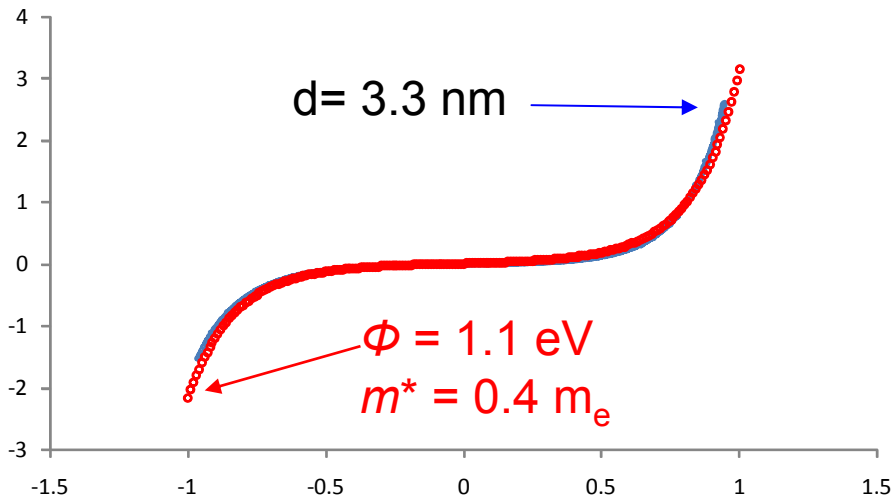
All common off-resonance tunneling mechanisms fail:



Tunneling with reduced electron mass (modified Simmons equation):

$$J = \frac{q}{4\pi^2 \eta d^2} \left\{ \left(\phi - \frac{qV}{2} \right) \times \exp \left[-\frac{2\sqrt{2m^*}}{\eta} \sqrt{\left(\phi - \frac{qV}{2} \right) d} \right] - \left(\phi + \frac{qV}{2} \right) \times \exp \left(-\frac{2\sqrt{(2m^*)}}{\eta} \sqrt{\left(\phi + \frac{qV}{2} \right) d} \right) \right\}$$

m^* = effective electron mass, where mass of charge carrier = $m^* \times 9.1 \times 10^{-31}$ kg



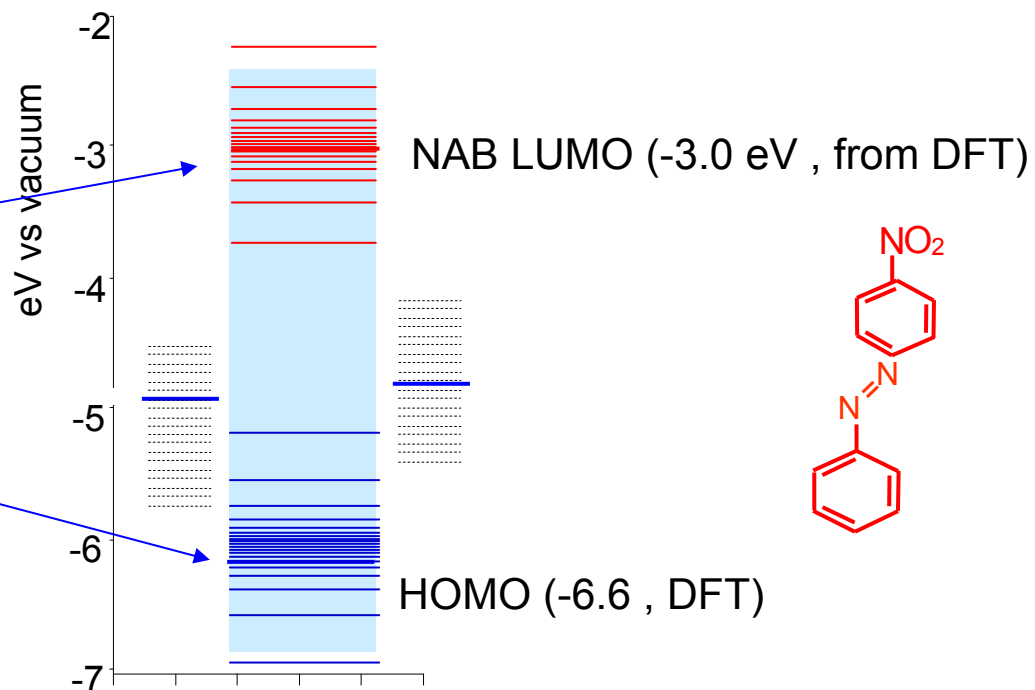
Experimental data collected at 5 or 6 K

“off resonant” tunneling just doesn’t work

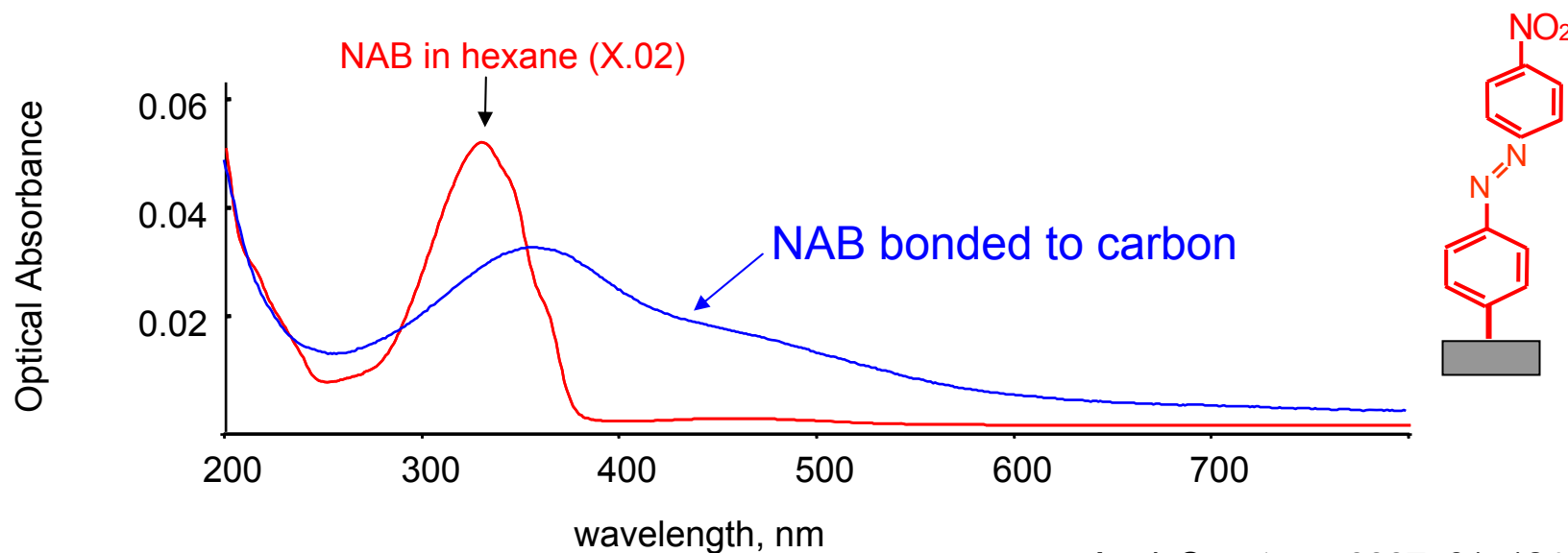
An alternative approach:

we expect these levels to be broadened, by:

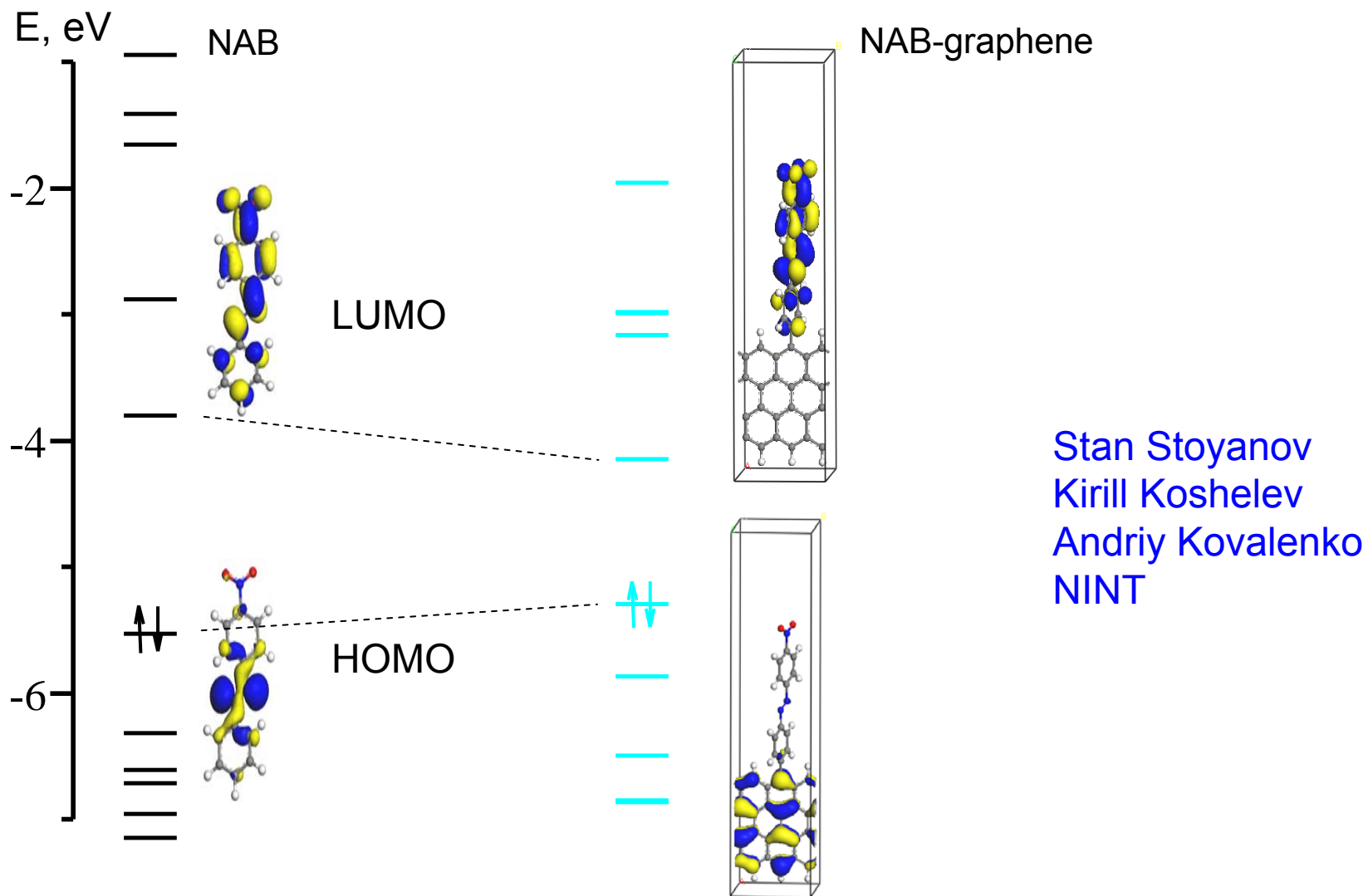
- electronic coupling to substrate
- intermolecular interactions
- variable bonding geometry
- uncertainty (i.e. lifetime) broadening



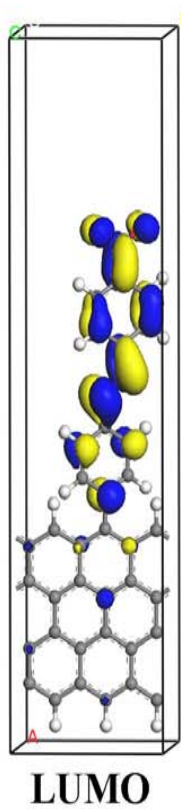
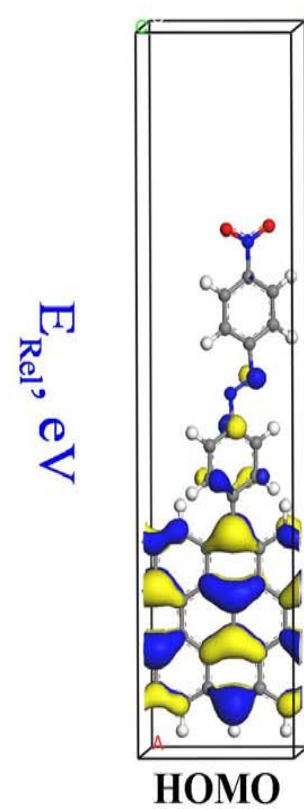
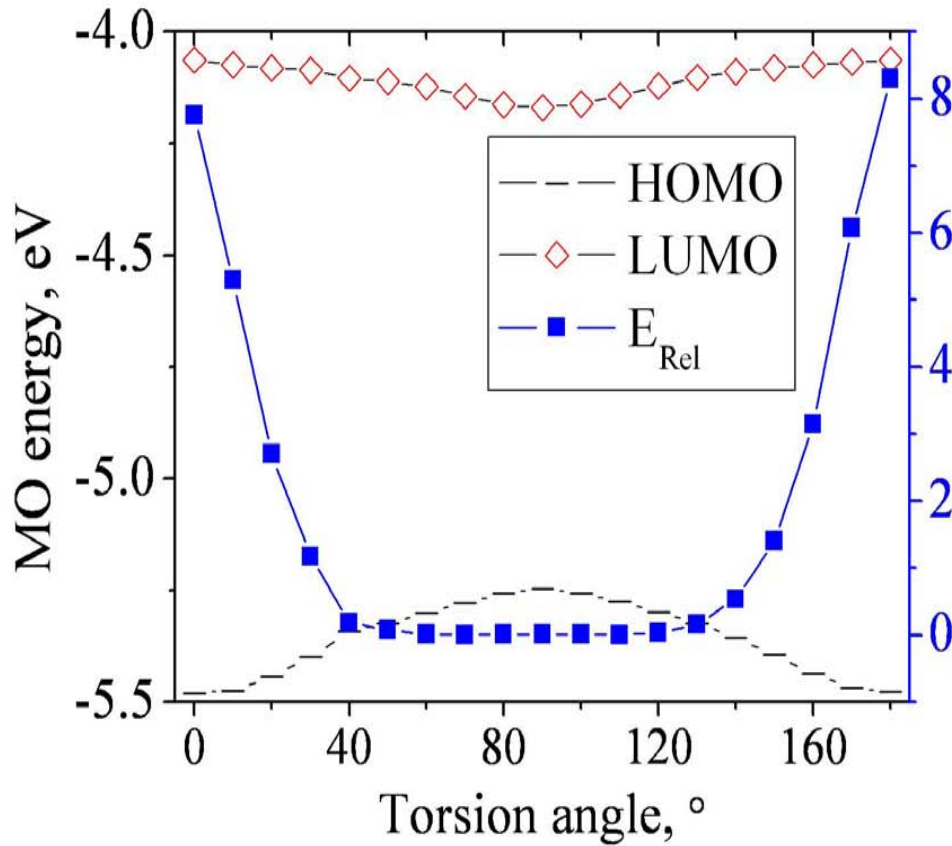
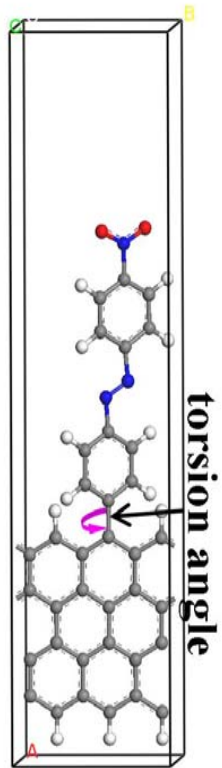
Some evidence for broadening:



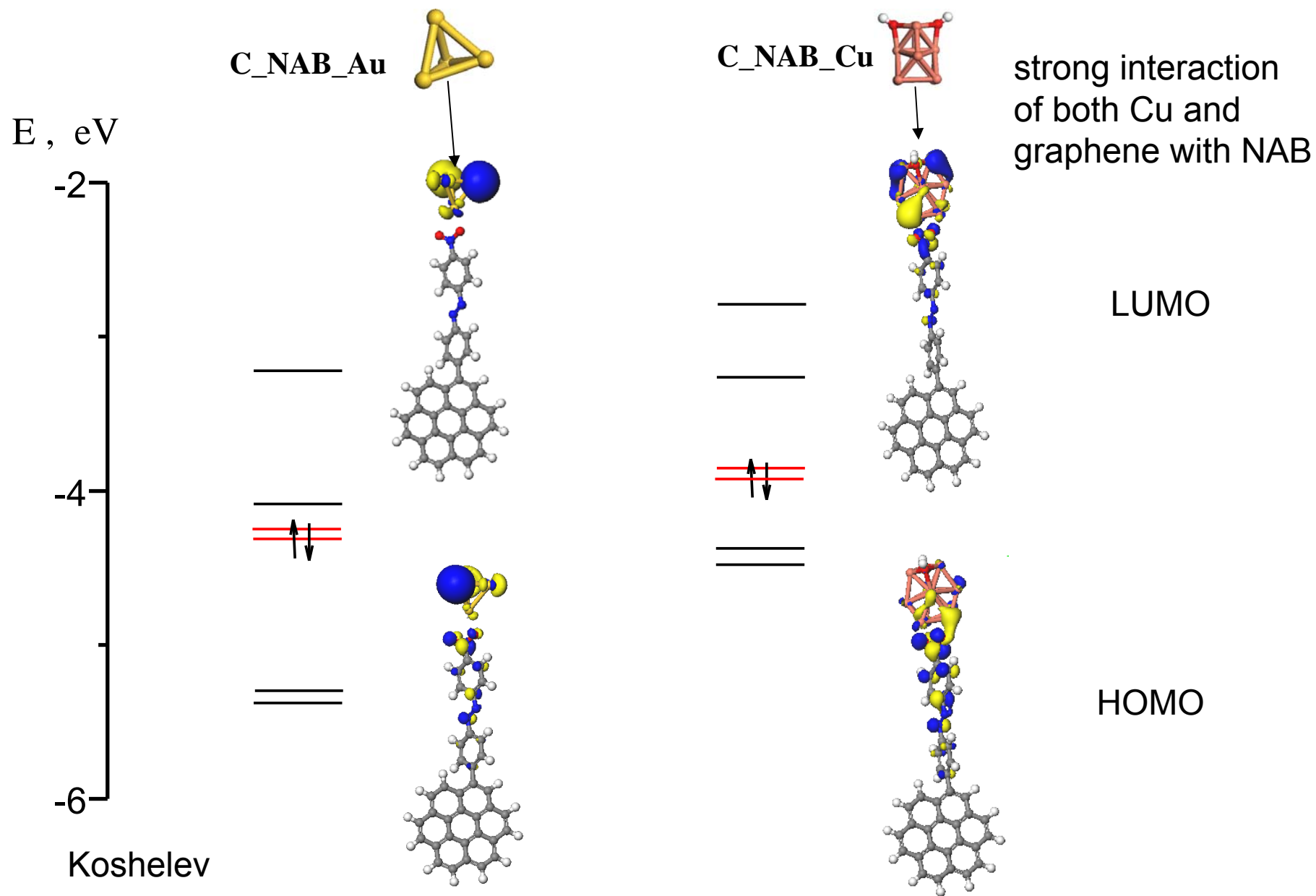
DFT with periodic boundary conditions for graphene



HOMO and LUMO energies vary with torsion angle

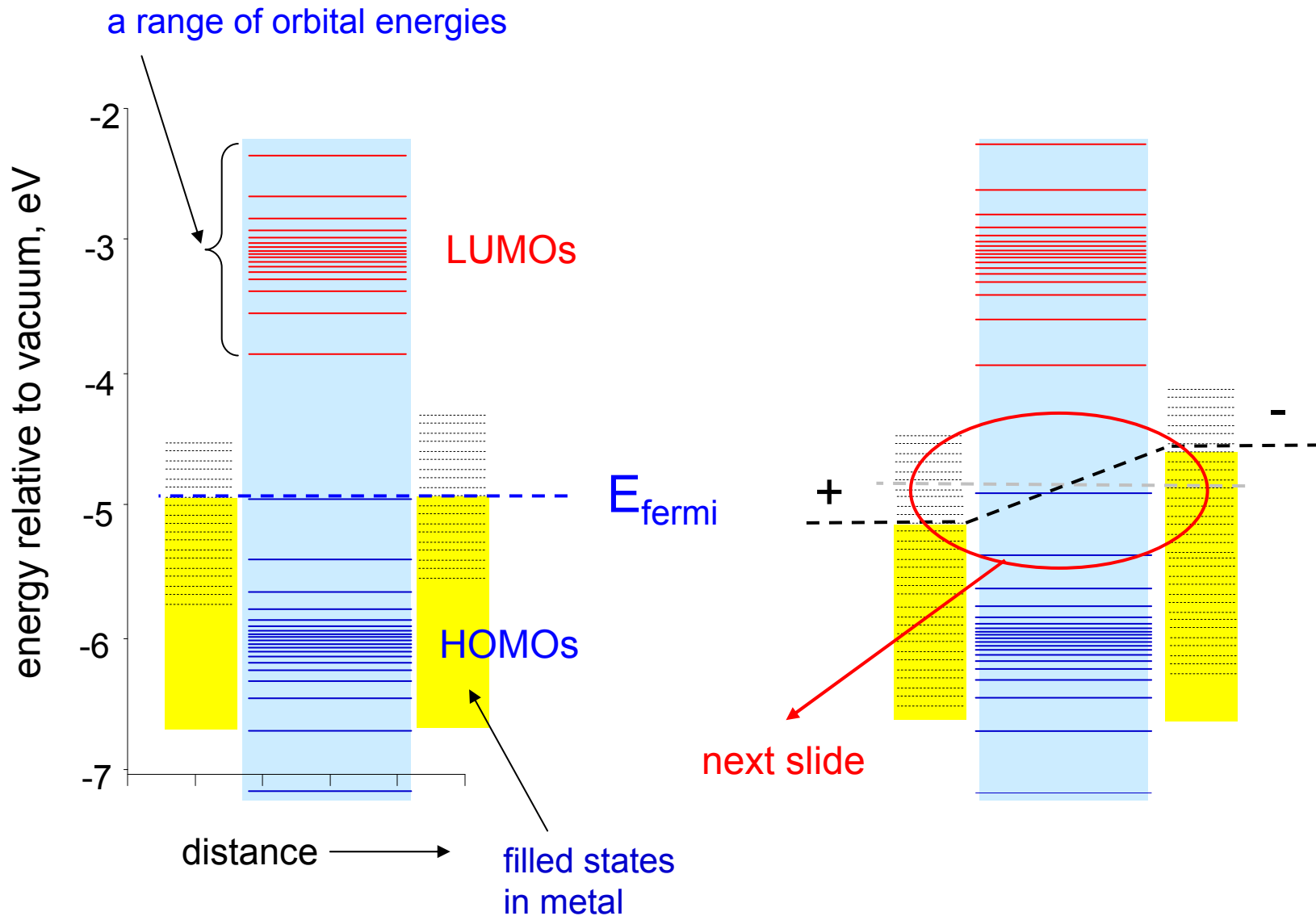


Modeling of both contacts and molecule



Zero bias:

positive bias:

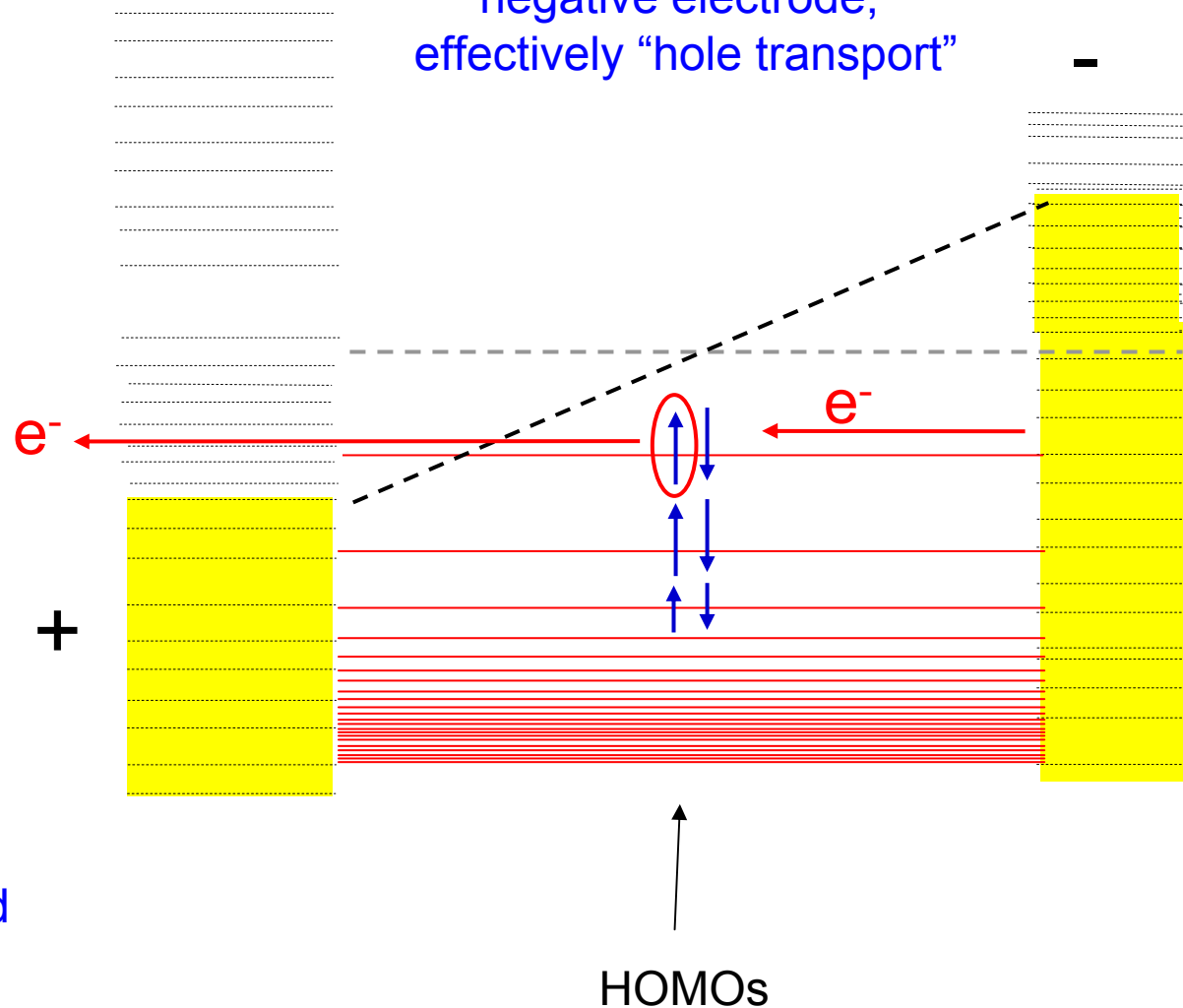


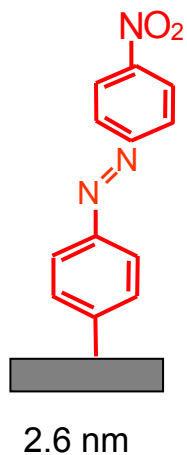
once + bias creates empty metal orbitals, electrons can leave HOMO

+ bias

Note that more HOMOs become accessible for higher bias, causing upward curvature

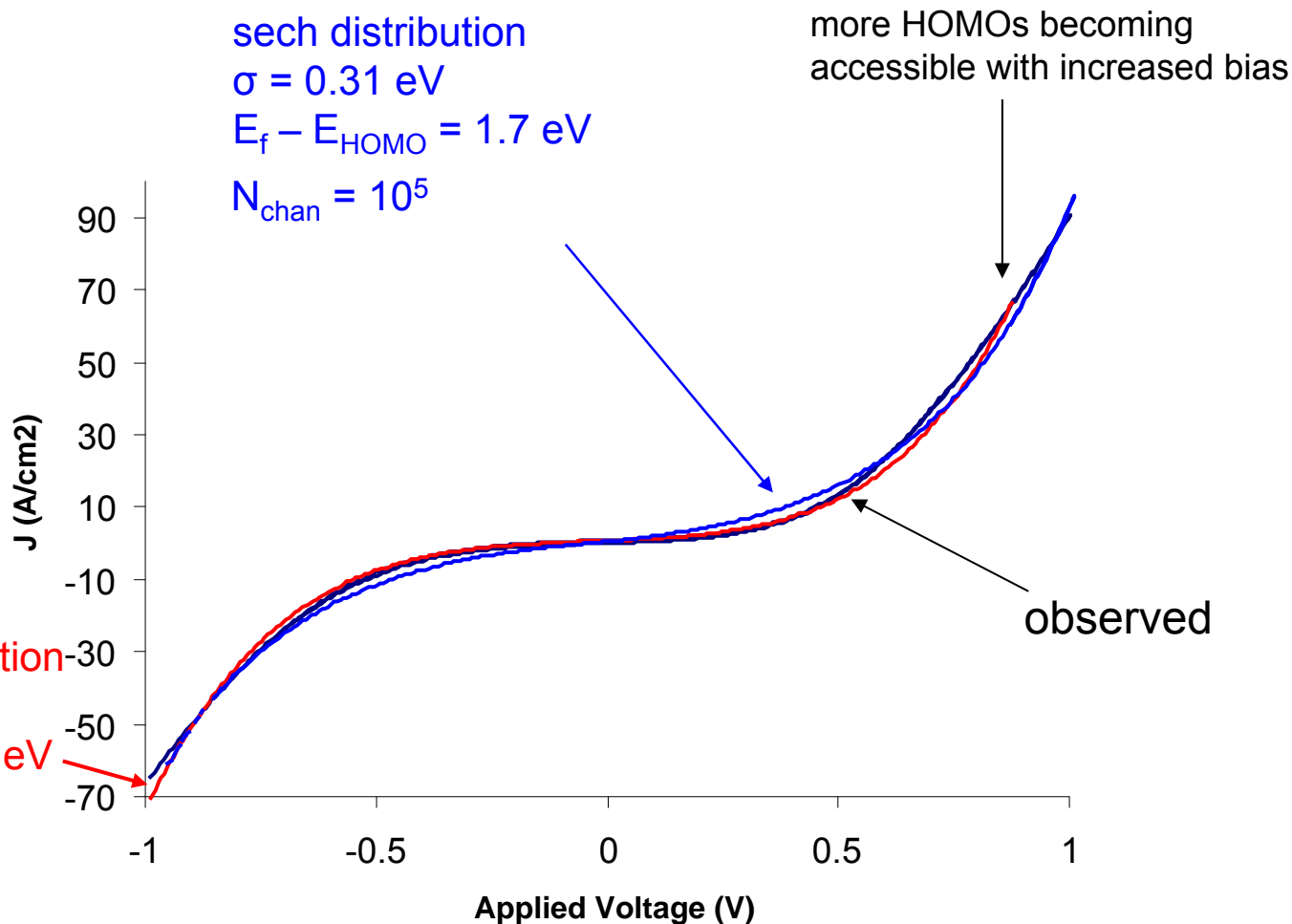
HOMO fills again from negative electrode, effectively "hole transport"





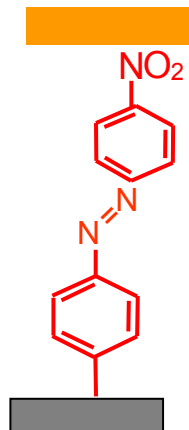
gaussian distribution
 $\sigma = 0.52 \text{ eV}$
 $E_f - E_{\text{HOMO}} = 1.7 \text{ eV}$
 $N_{\text{chan}} = 10^5$

sech distribution
 $\sigma = 0.31 \text{ eV}$
 $E_f - E_{\text{HOMO}} = 1.7 \text{ eV}$
 $N_{\text{chan}} = 10^5$

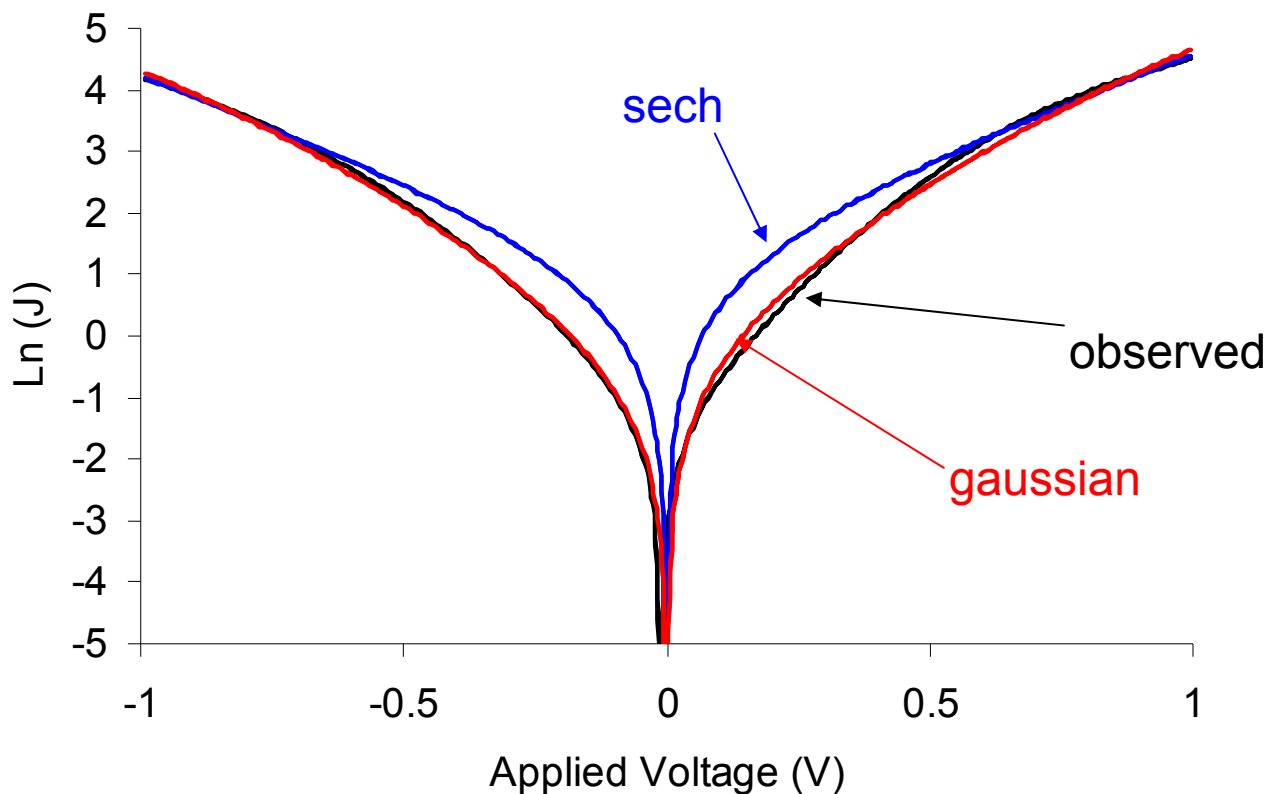


σ = half width of orbital energy distribution
 $E_f - E_{\text{HOMO}}$ = Fermi level to orbital offset
 N_{chan} = total number of active channels

Sergio Jimenez
 Adam Bergren



PPF/NAB (2.6 nm)/Cu



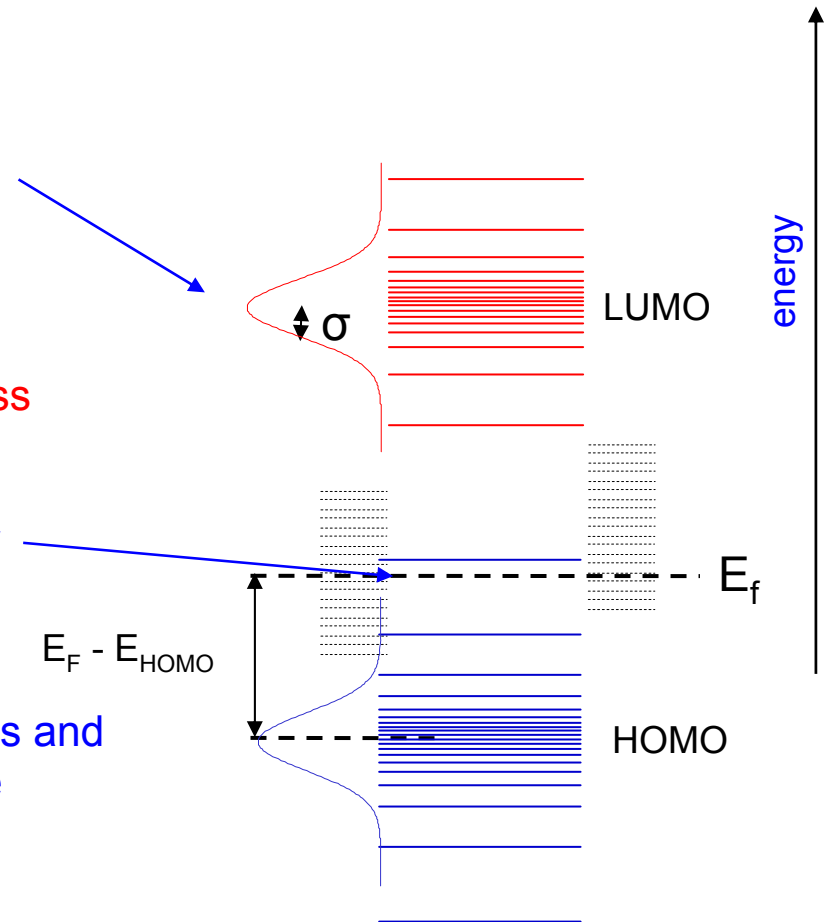
Main parameters of the model:

- $E_f - E_{\text{HOMO}}$
- HOMO "linewidth" (σ)
- and number of channels (N)
- molecular layer thickness (d)

for the electrochemists:
 NOT Marcus/Butler-Volmer;
 similarity due to distribution
 of orbital energies rather
 than thermal fluctuations

Important notes:

- broadening caused by coupling and local environment, not thermal fluctuations
- main parameters are distribution width (σ), energy offset ($E_F - E_{\text{HOMO}}$), and thickness
- overlap of metal and molecule orbitals may (and probably does) occur at zero bias
- depending on offset between molecular orbitals and Fermi level, we can greatly vary conductance



The punch line: strong interactions between molecule and contacts result in *resonant* electron transport rather than classical tunneling

Adam Bergren (NRC)
Sergio Jimenez (visit. prof.)
Andriy Kovalenko
Stan Stoyanov
Kirill Koshelev
Jie Ru (Uof Alberta)
Bryan Szeto

} NINT

Also :

Rory Chisholm (2:00 PM Monday)
Mark McDermott

